

FIG. 1
RELATED ART

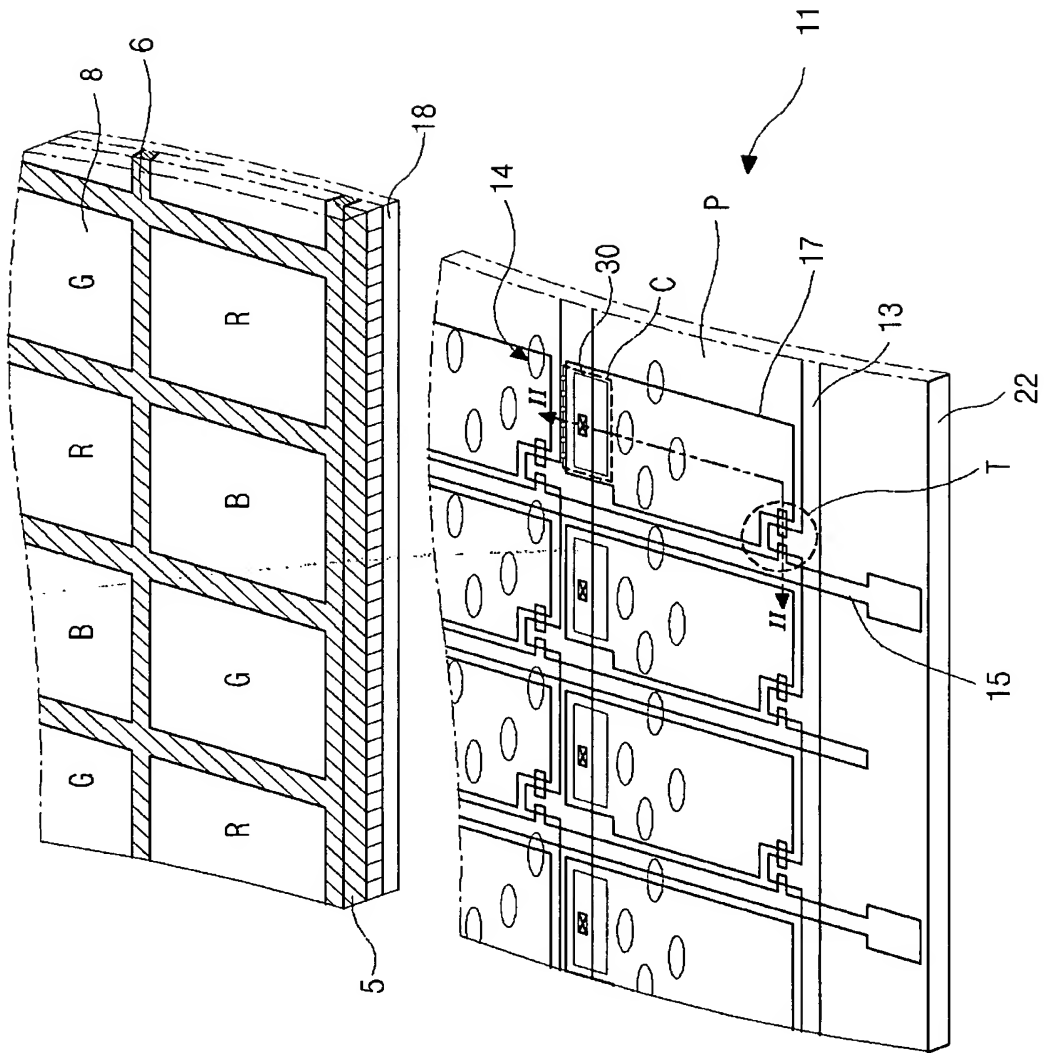


FIG. 2
RELATED ART

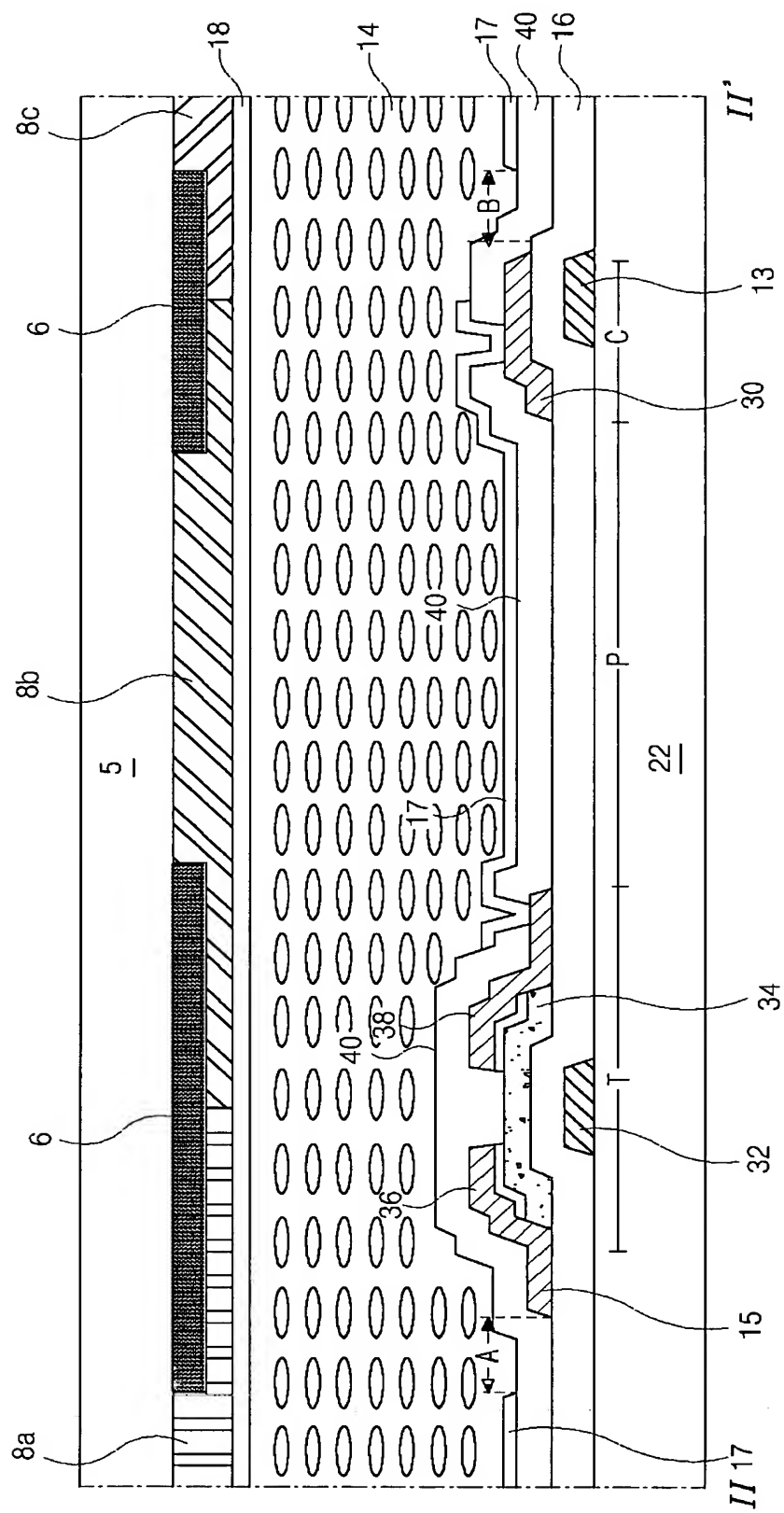


FIG. 3

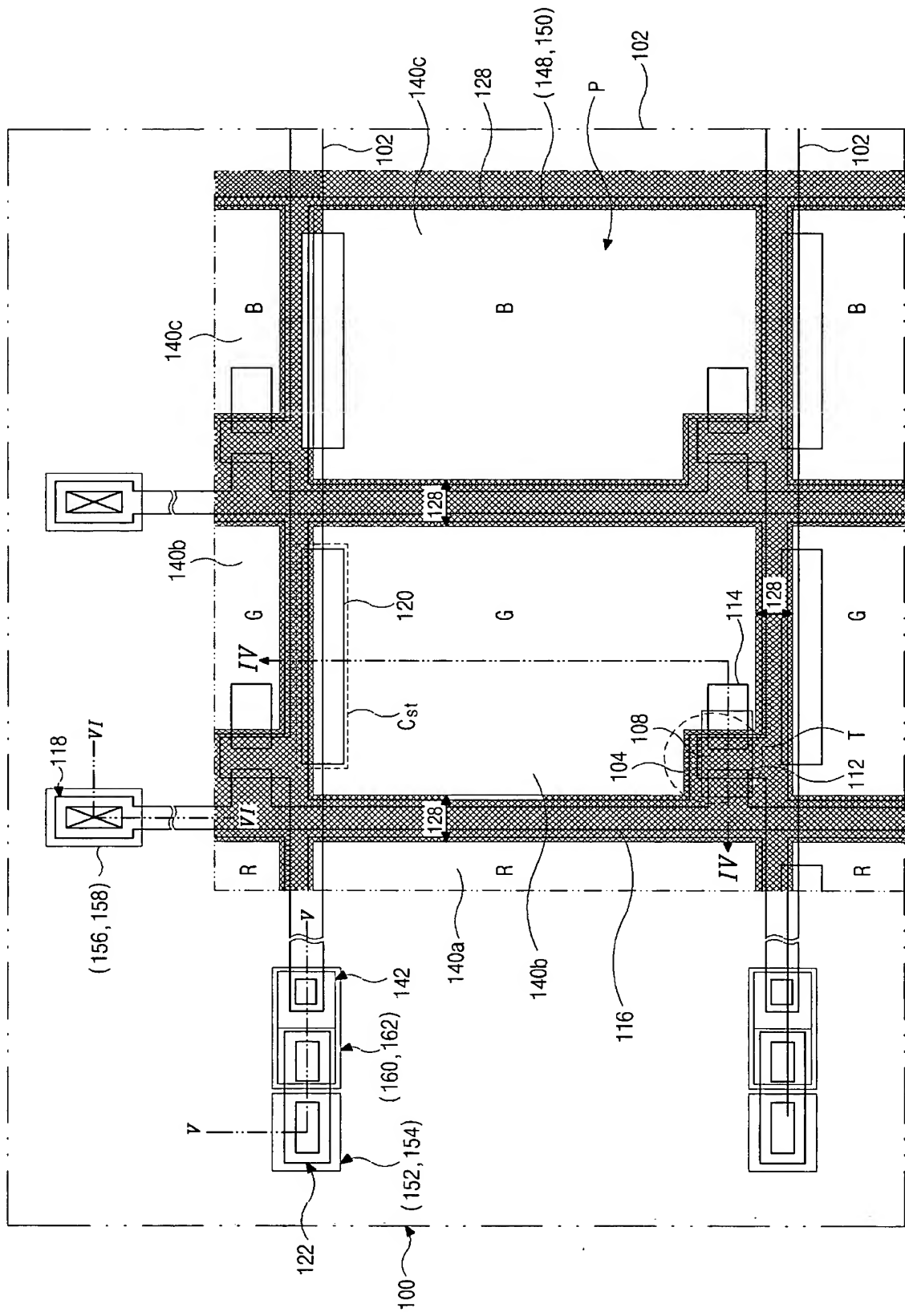
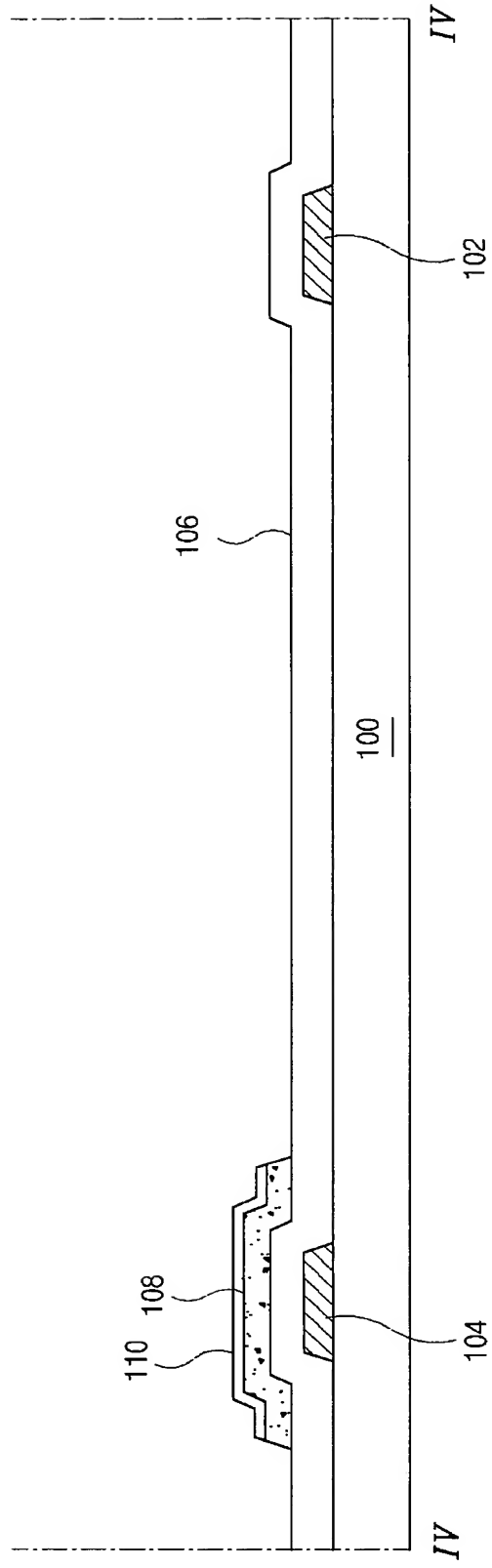


FIG. 4A



This cross-sectional view shows a substrate 100 with a top layer 102. A central region 104 is defined by a width T . On the left side, a series of layers are shown: 116, 112, 108, 110, and 114. A layer 124 is located between the central region 104 and the left-side layers. On the right side, a layer 120 is shown, with a width C_{st} indicated. A dashed line labeled *IV* is on the far right, and another dashed line labeled *IV* is on the far left, indicating the plane of the cross-section.

FIG. 4D

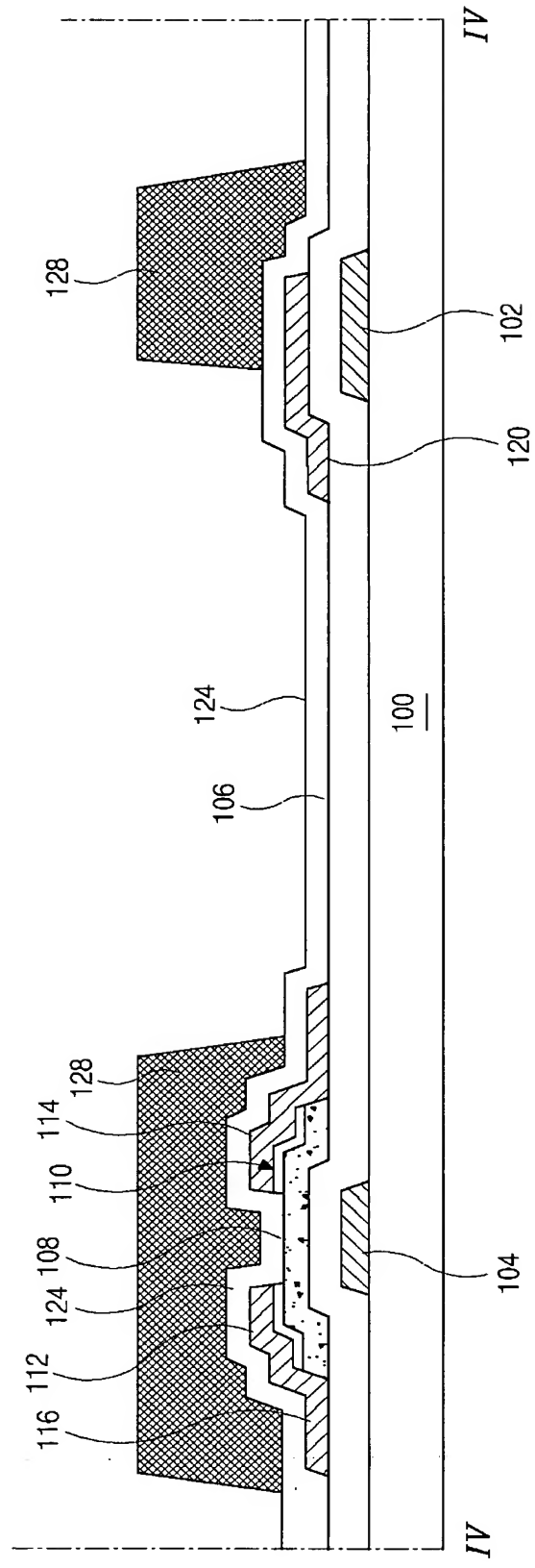


FIG. 4E

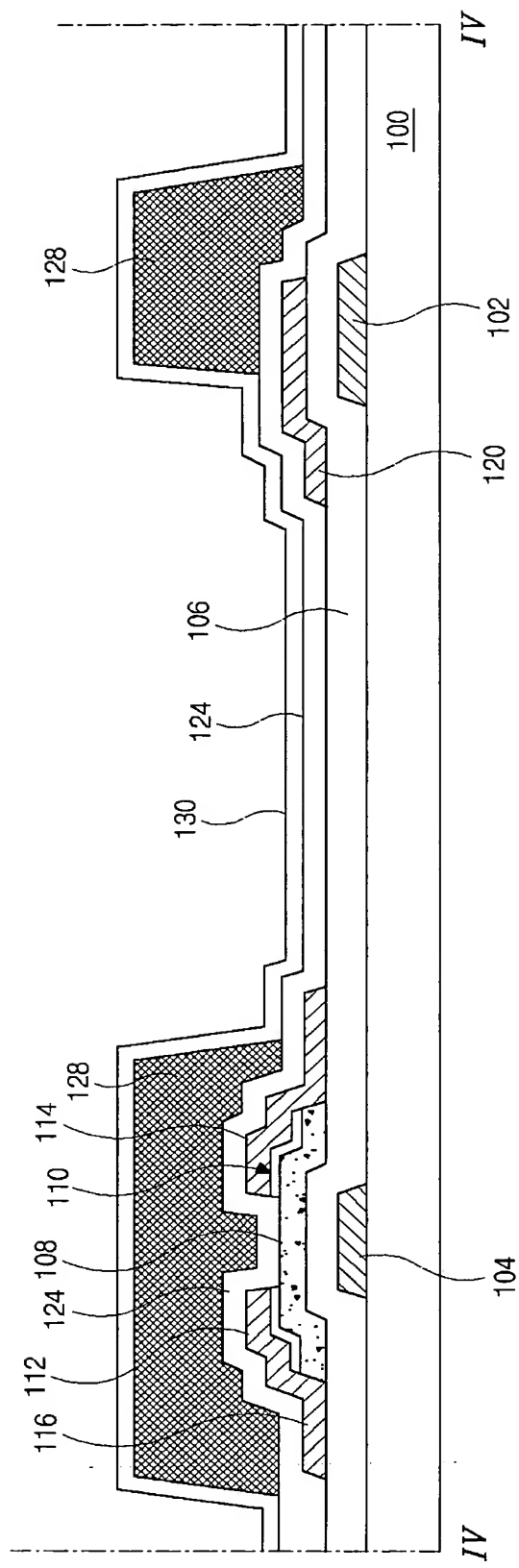


FIG. 4F

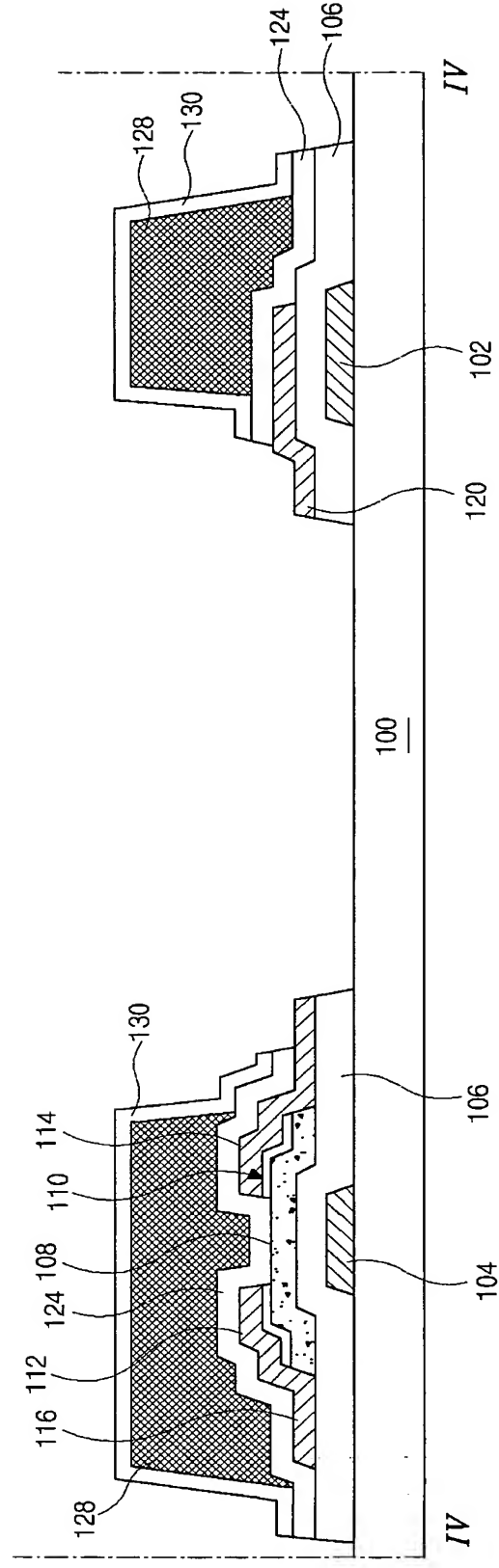


FIG. 4G

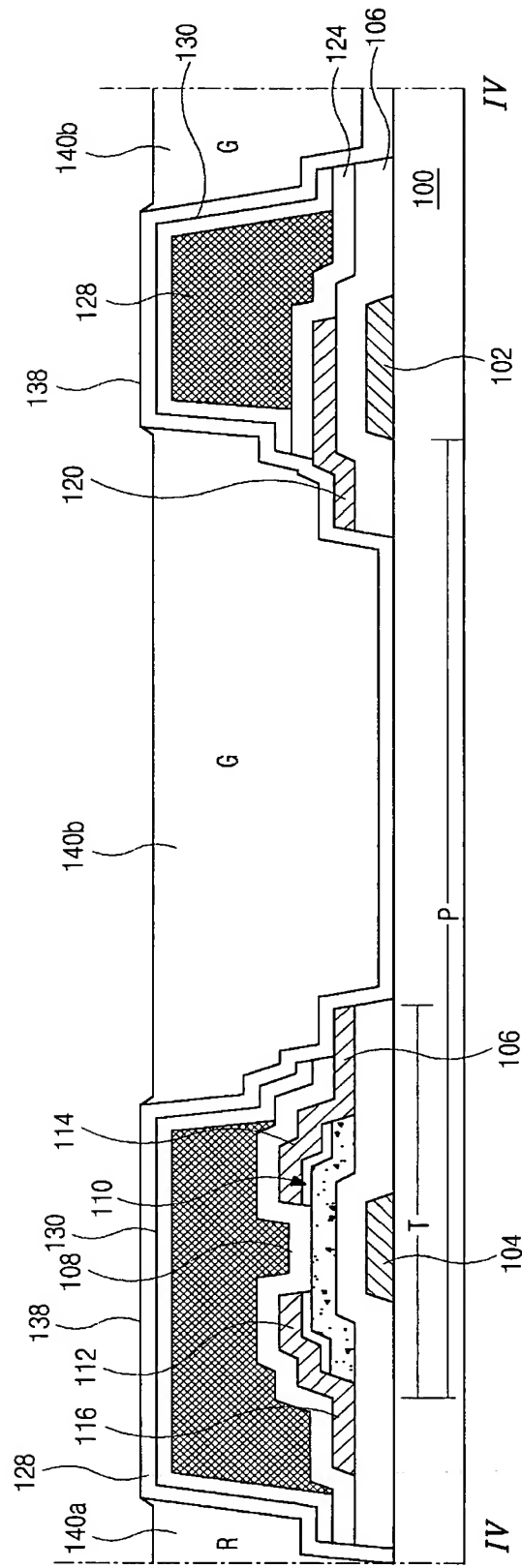


FIG. 4H

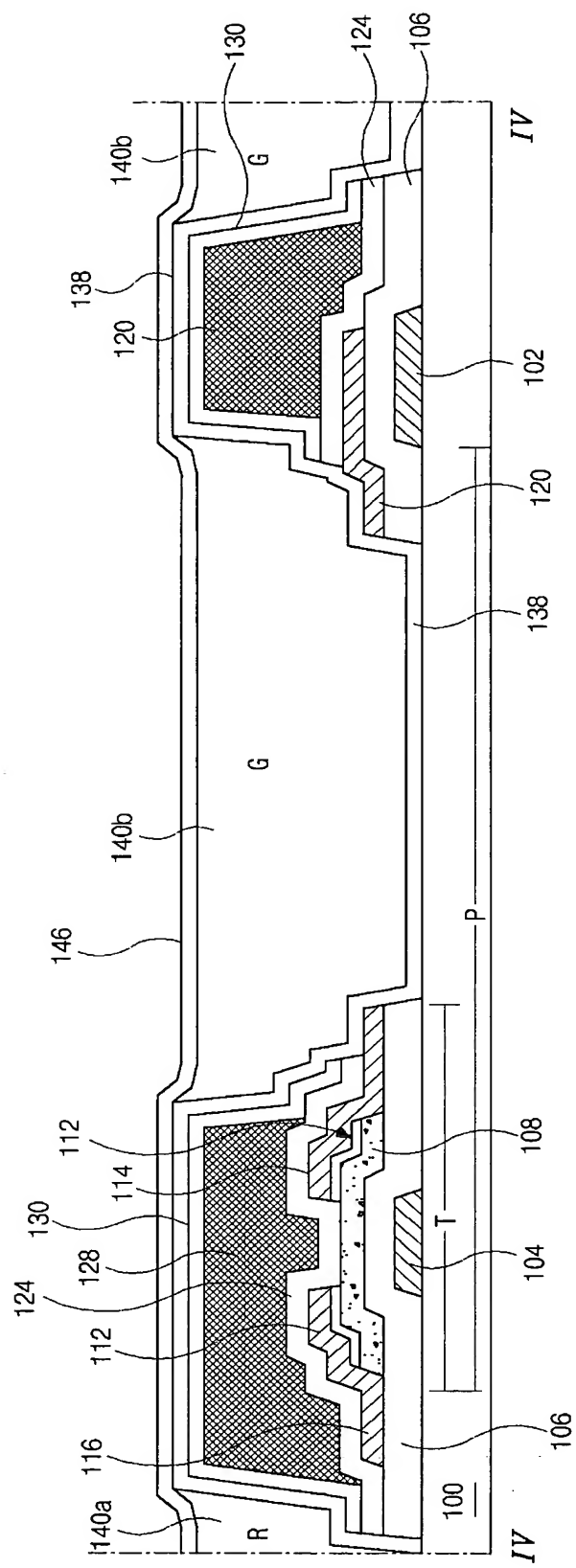


FIG. 4I

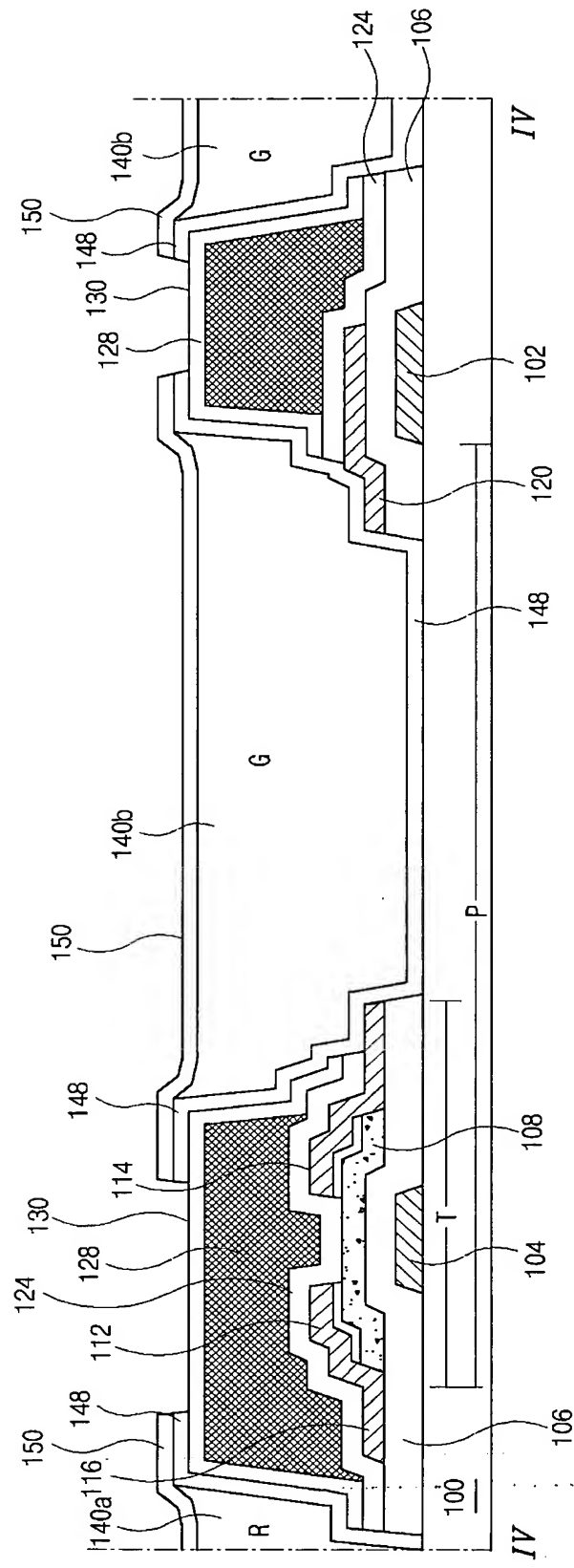


FIG. 5A

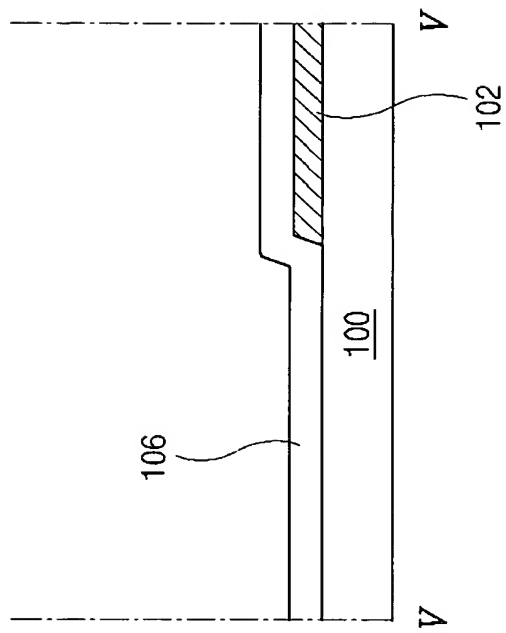


FIG. 5B

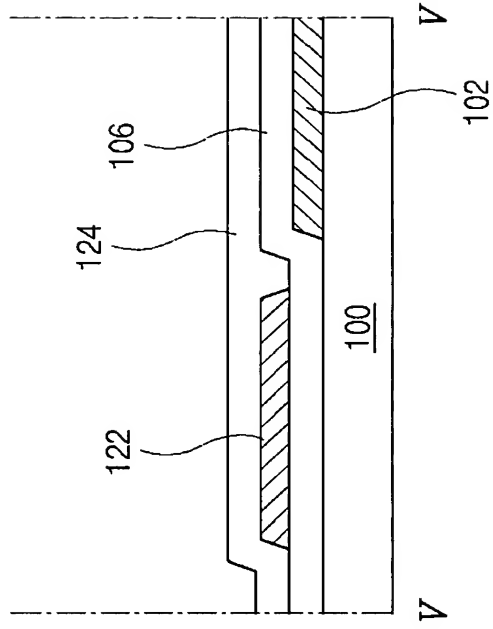


FIG. 5C

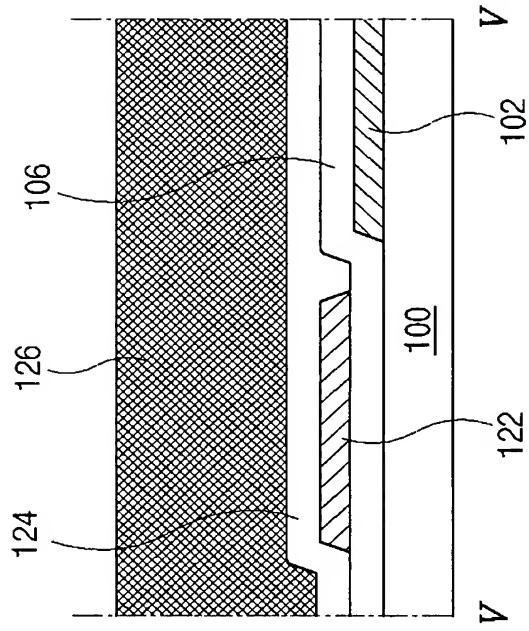


FIG. 5D

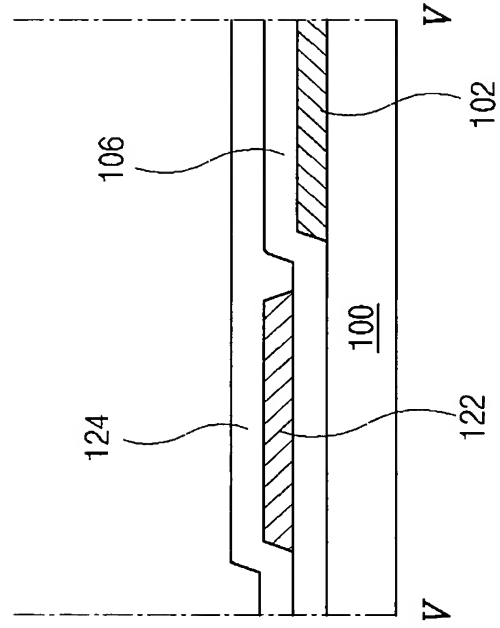


FIG. 5E

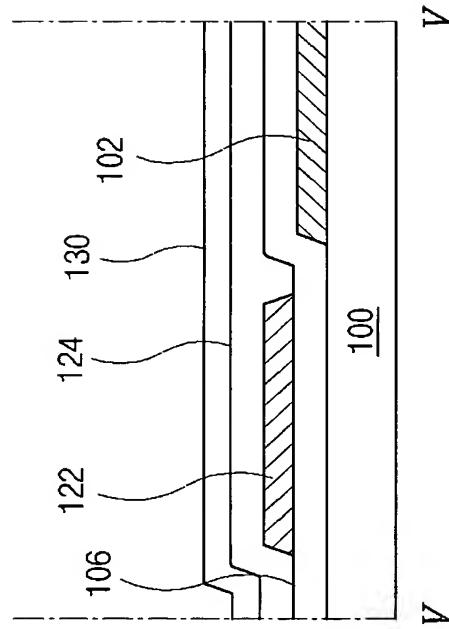


FIG. 5G

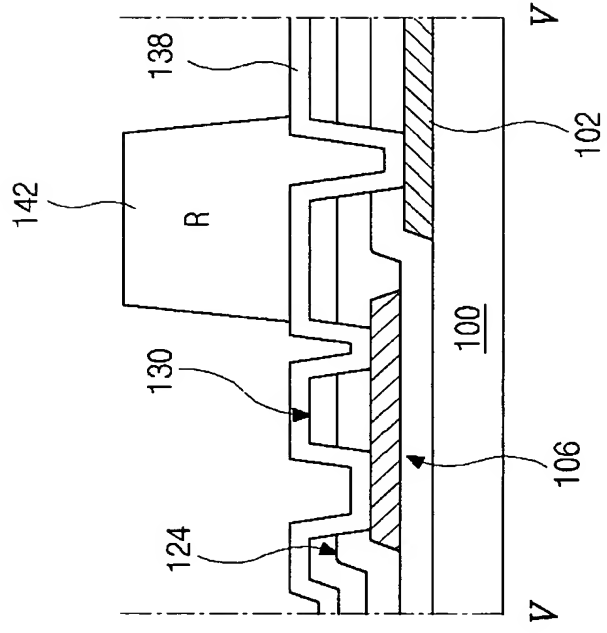


FIG. 5H

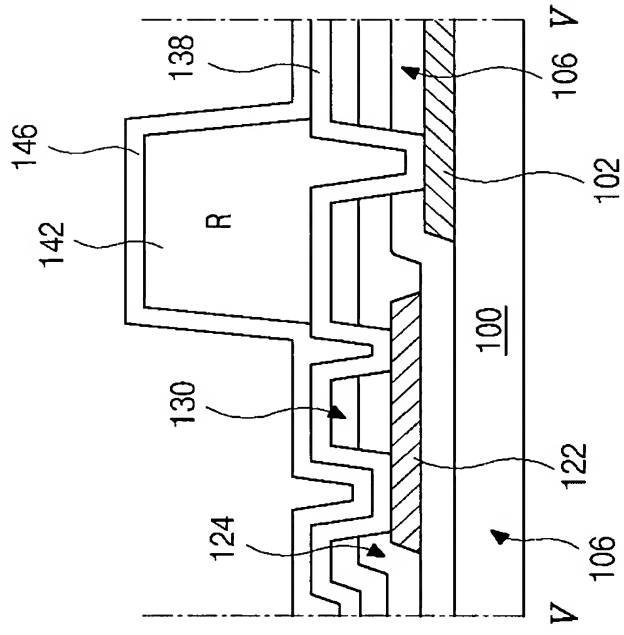


FIG. 51

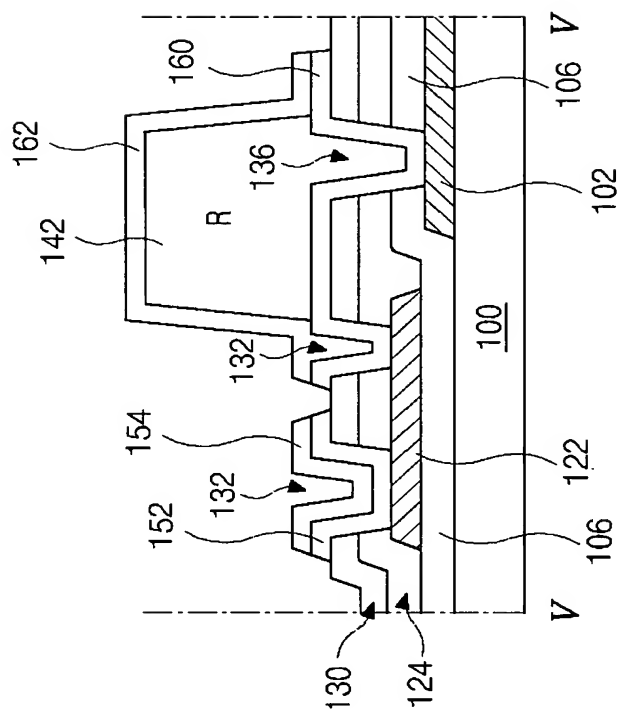


FIG. 6A

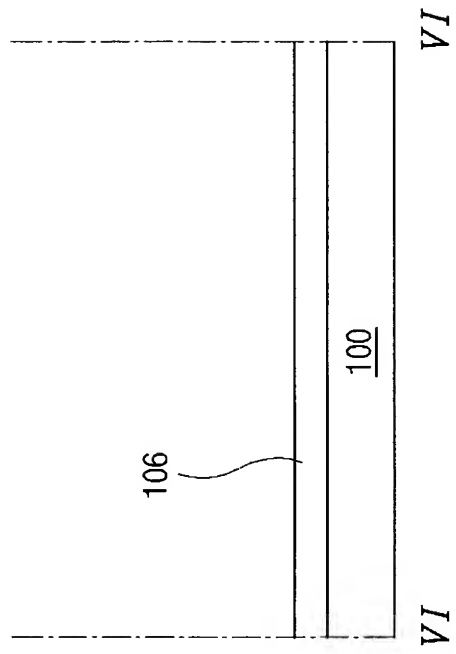


FIG. 6B

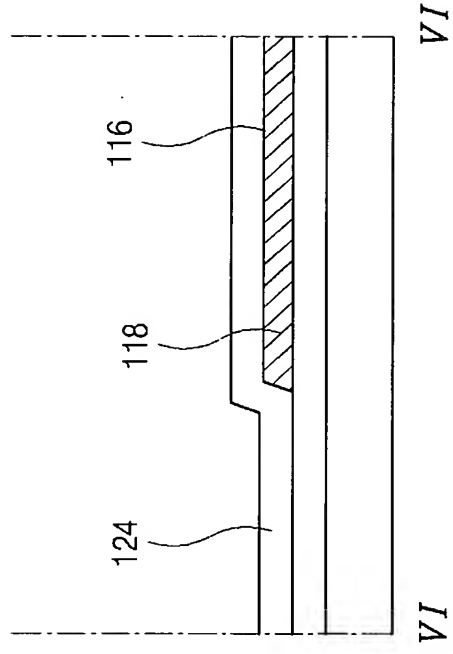


FIG. 6C

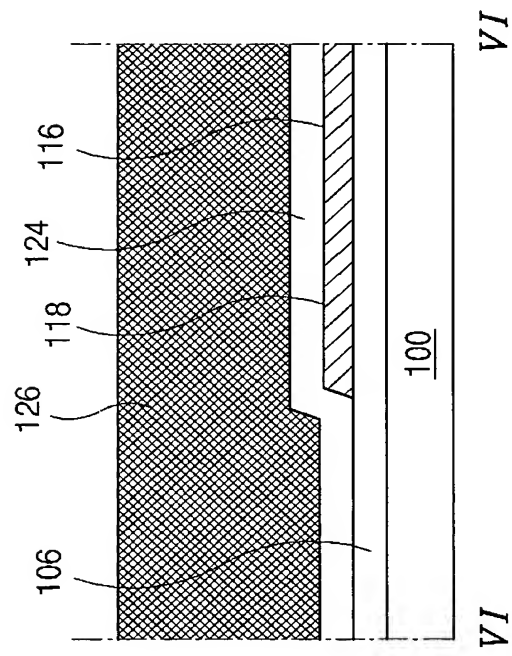


FIG. 6D

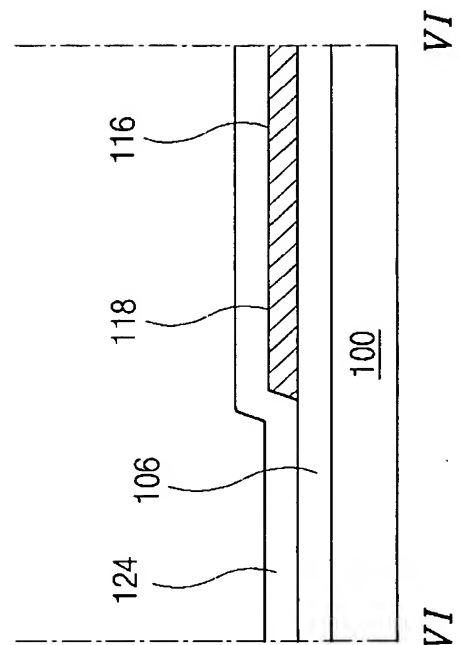


FIG. 6E

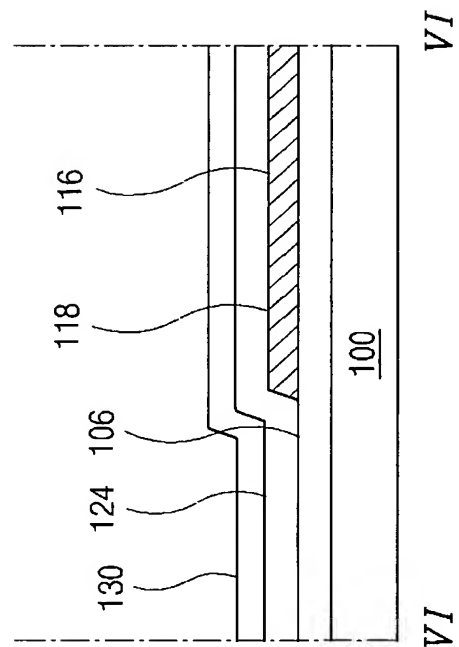


FIG. 6F

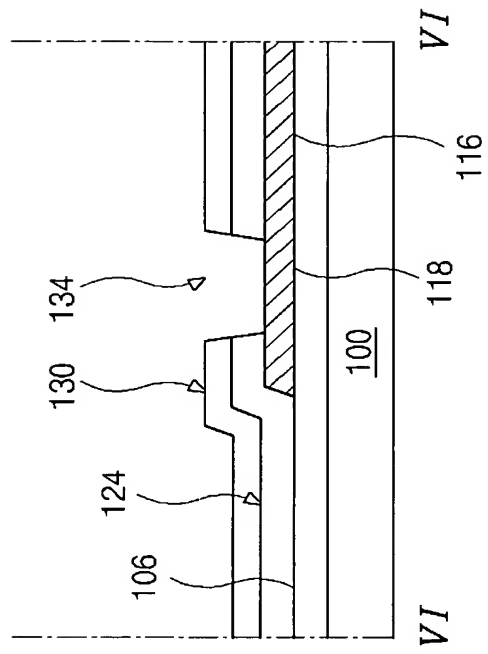


FIG. 6G.

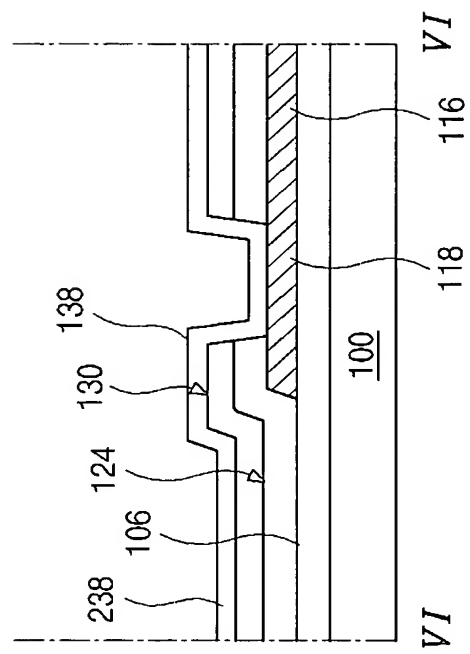


FIG. 6H

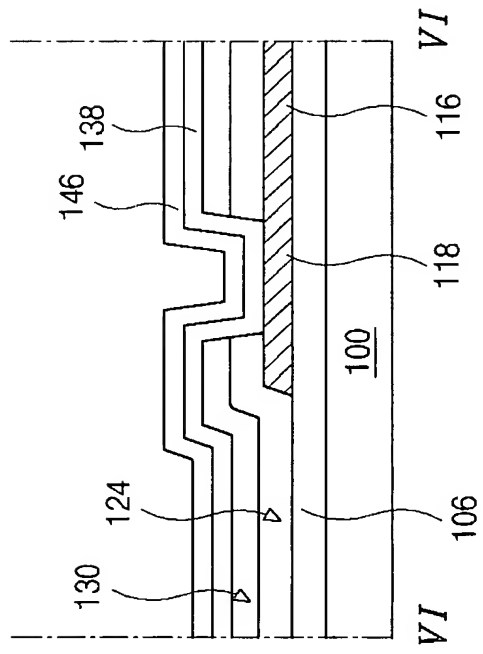


FIG. 6I

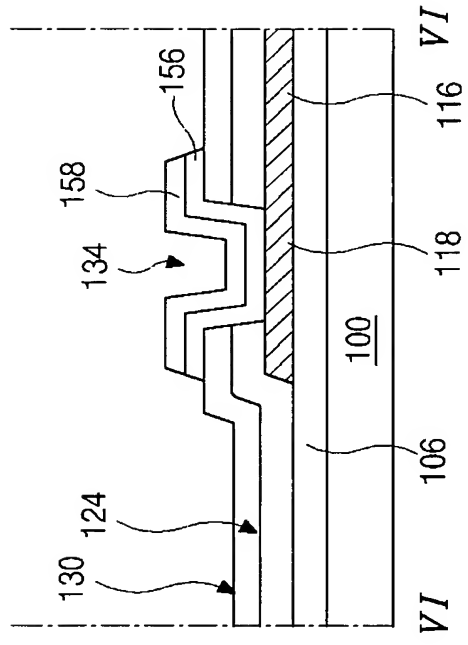


FIG. 7

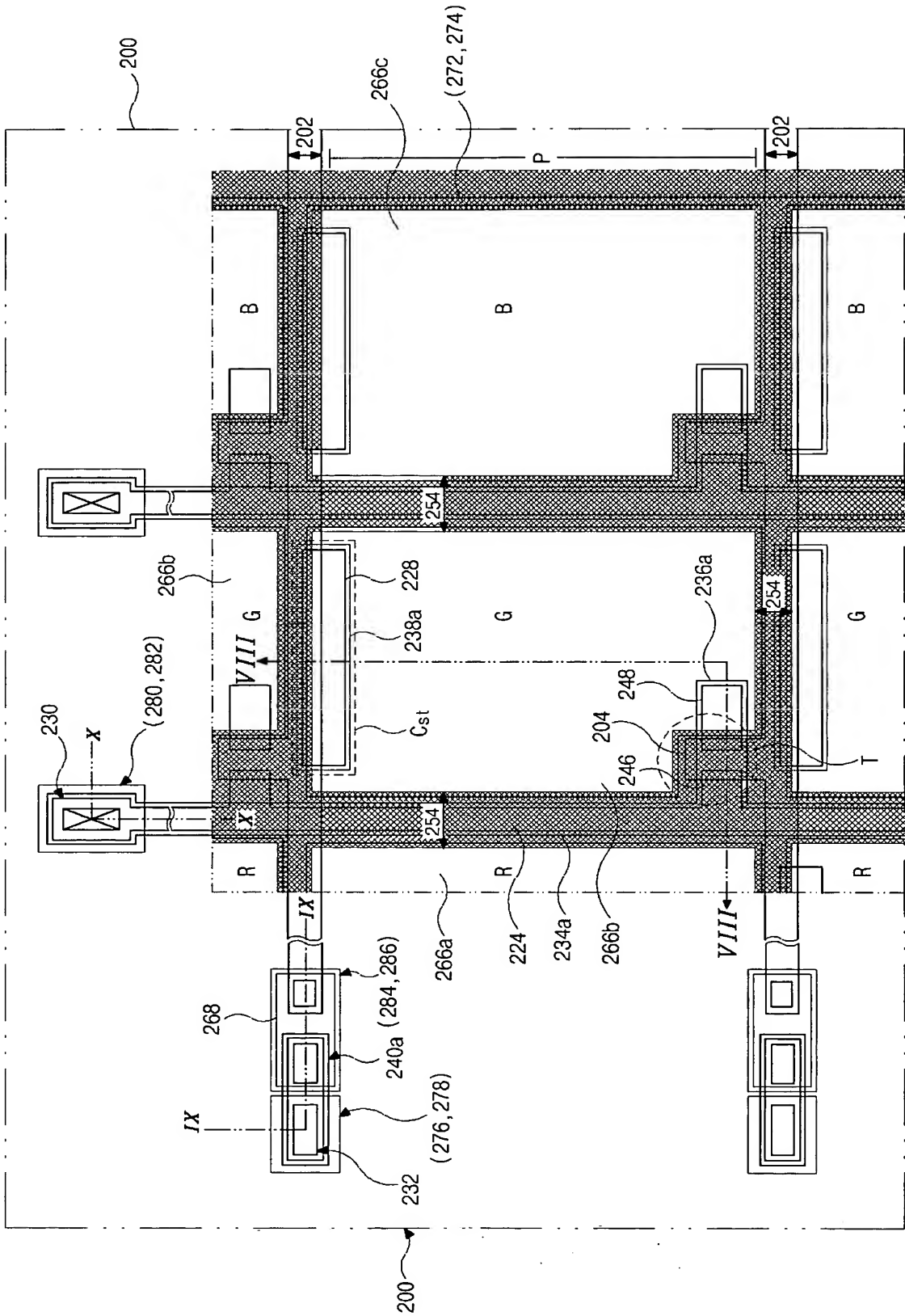


FIG. 8A

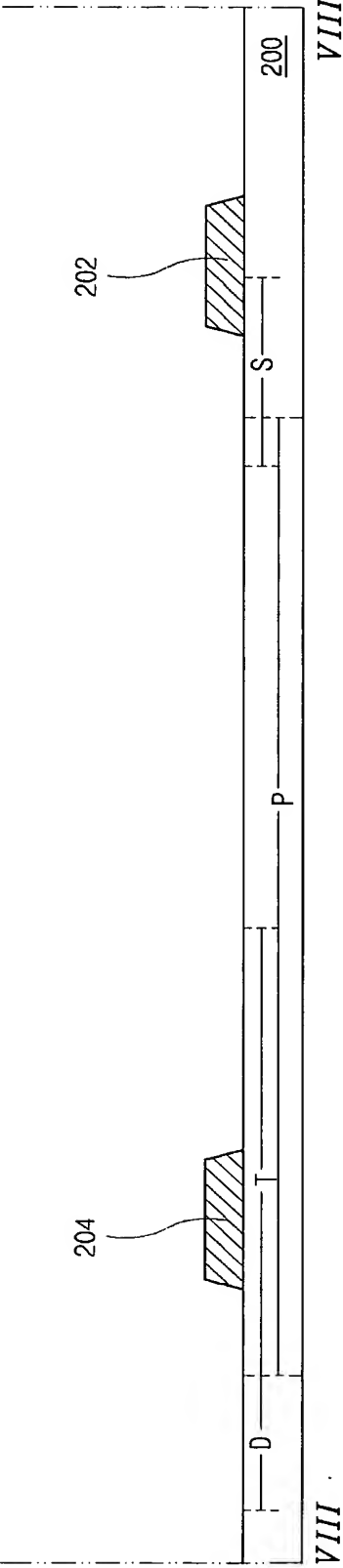


FIG. 8B

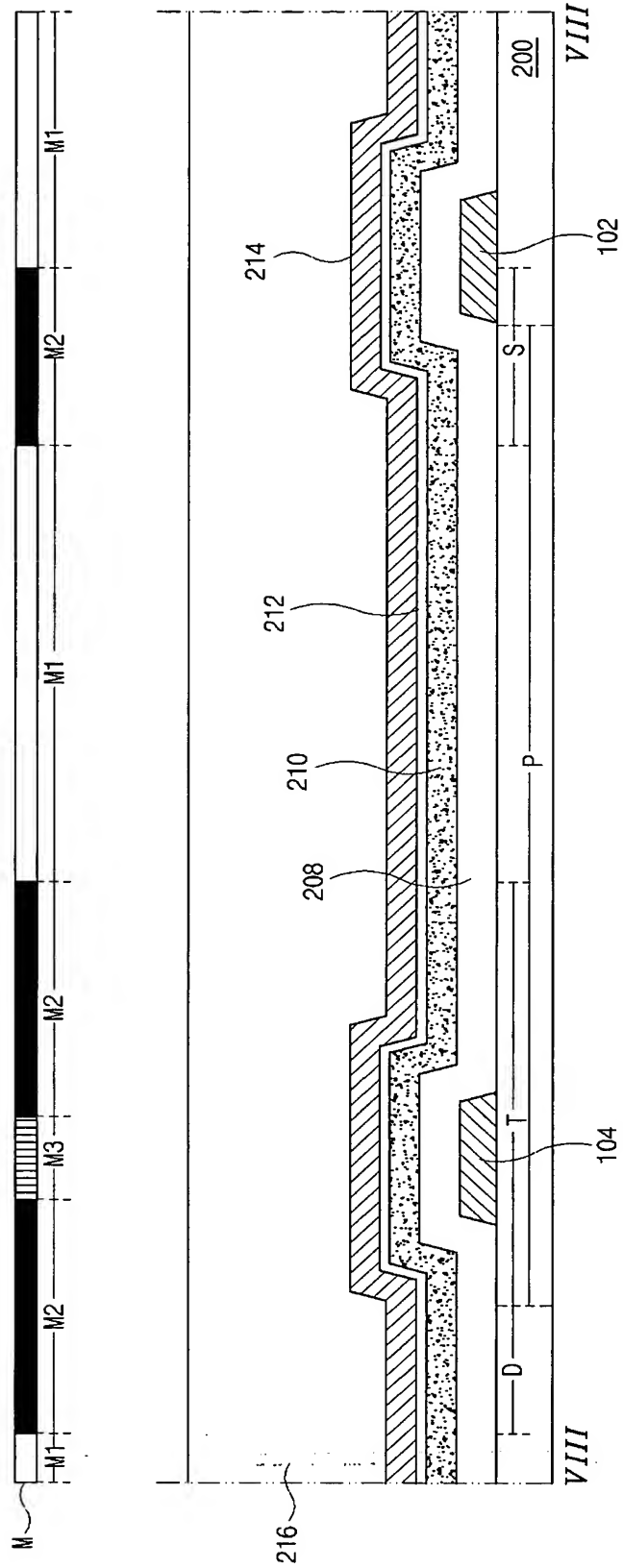


FIG. 8.

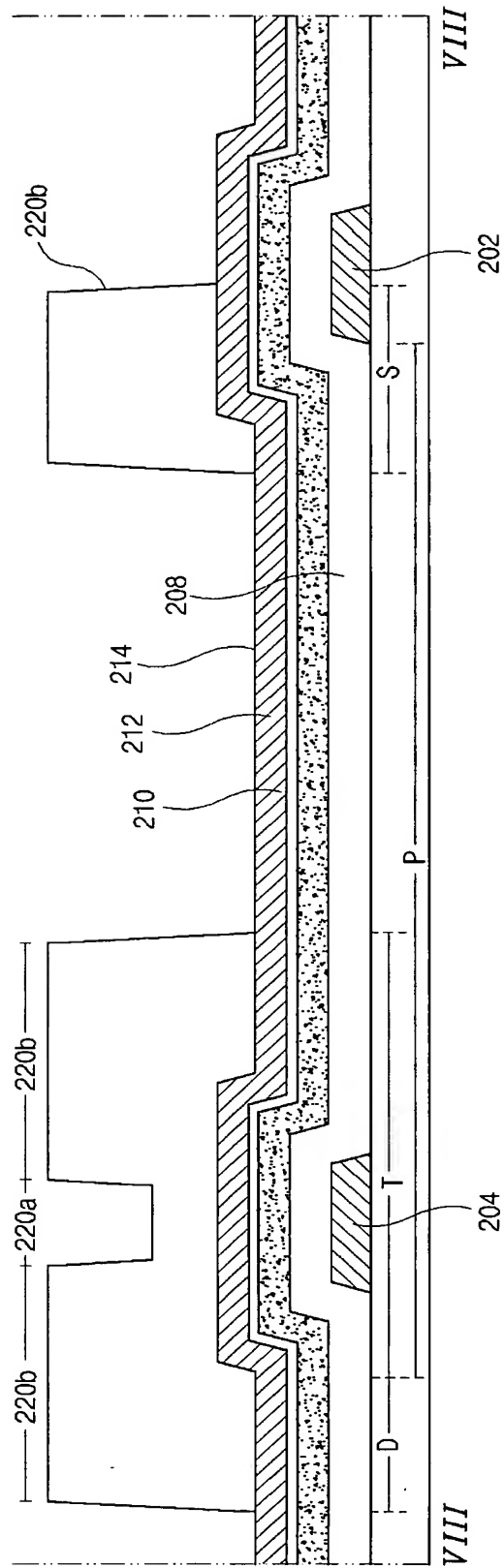
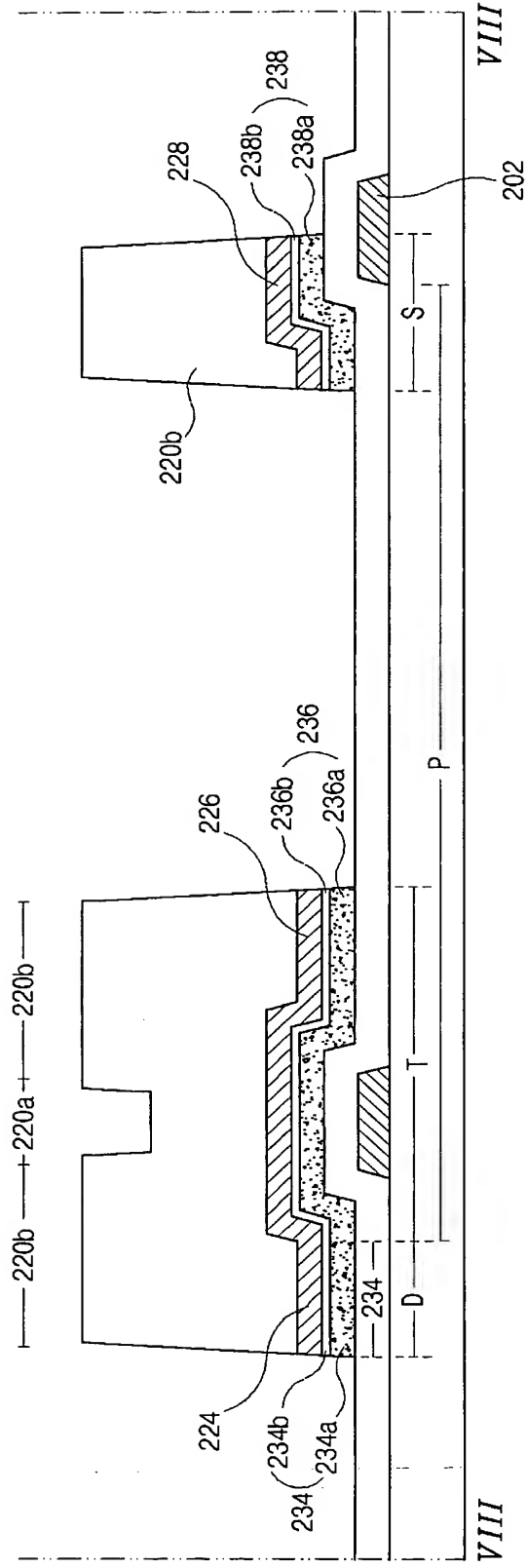


FIG. 8D



This diagram shows a cross-sectional view of a semiconductor device. It features two transistors on a common substrate 202. The first transistor on the left has a gate stack 224, a gate 226, and a channel region 234. The channel region 234 is divided into two parts, 234a and 234b, by a vertical interface 236. The second transistor on the right has a gate stack 228, a gate 230, and a channel region 238. The channel region 238 is divided into two parts, 238a and 238b, by a vertical interface 236. The device includes various layers and regions labeled with reference numerals: 202 (substrate), 204 (insulating layer), 208 (silicon layer), 210 (silicon layer), 212 (silicon layer), 214 (silicon layer), 216 (silicon layer), 218 (silicon layer), 220 (silicon layer), 222 (silicon layer), 224 (gate stack), 226 (gate), 228 (gate stack), 230 (gate), 232 (silicon layer), 234 (channel region), 236 (vertical interface), 238 (channel region), 240 (silicon layer), 242 (silicon layer), 244 (silicon layer), 246 (silicon layer), 248 (silicon layer), 250 (silicon layer), 252 (silicon layer), 254 (silicon layer), 256 (silicon layer), 258 (silicon layer), 260 (silicon layer), 262 (silicon layer), 264 (silicon layer), 266 (silicon layer), 268 (silicon layer), 270 (silicon layer), 272 (silicon layer), 274 (silicon layer), 276 (silicon layer), 278 (silicon layer), 280 (silicon layer), 282 (silicon layer), 284 (silicon layer), 286 (silicon layer), 288 (silicon layer), 290 (silicon layer), 292 (silicon layer), 294 (silicon layer), 296 (silicon layer), 298 (silicon layer), 300 (silicon layer).

[illegible]

FIG. 8G

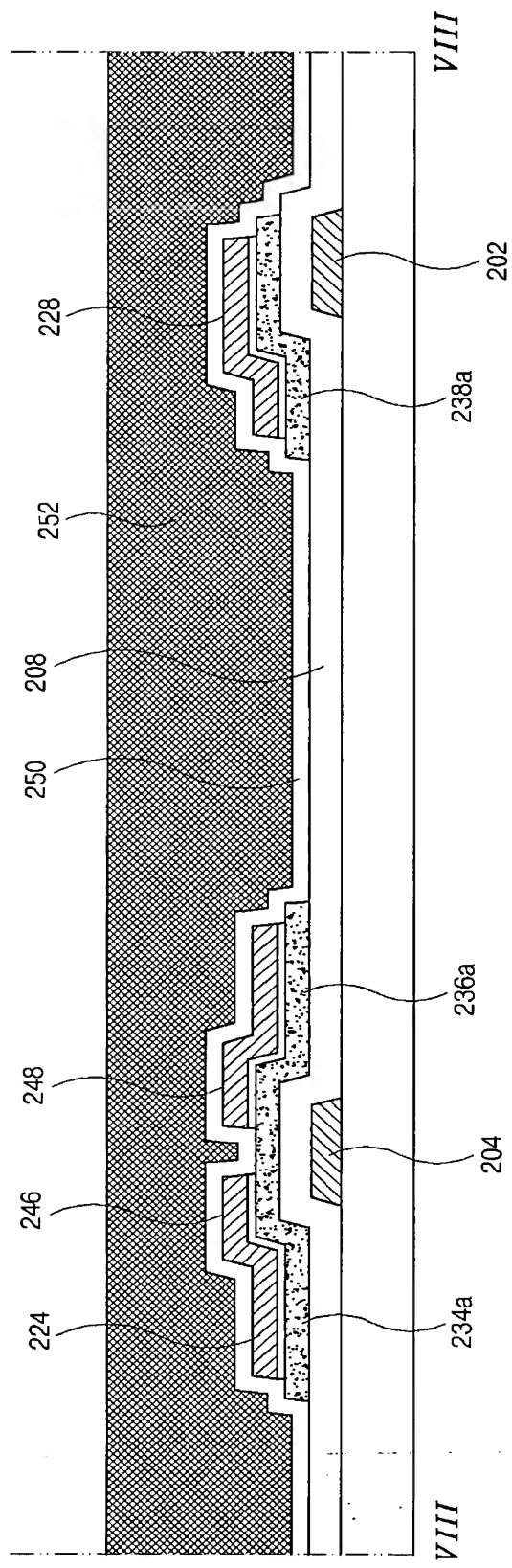


FIG. 8H

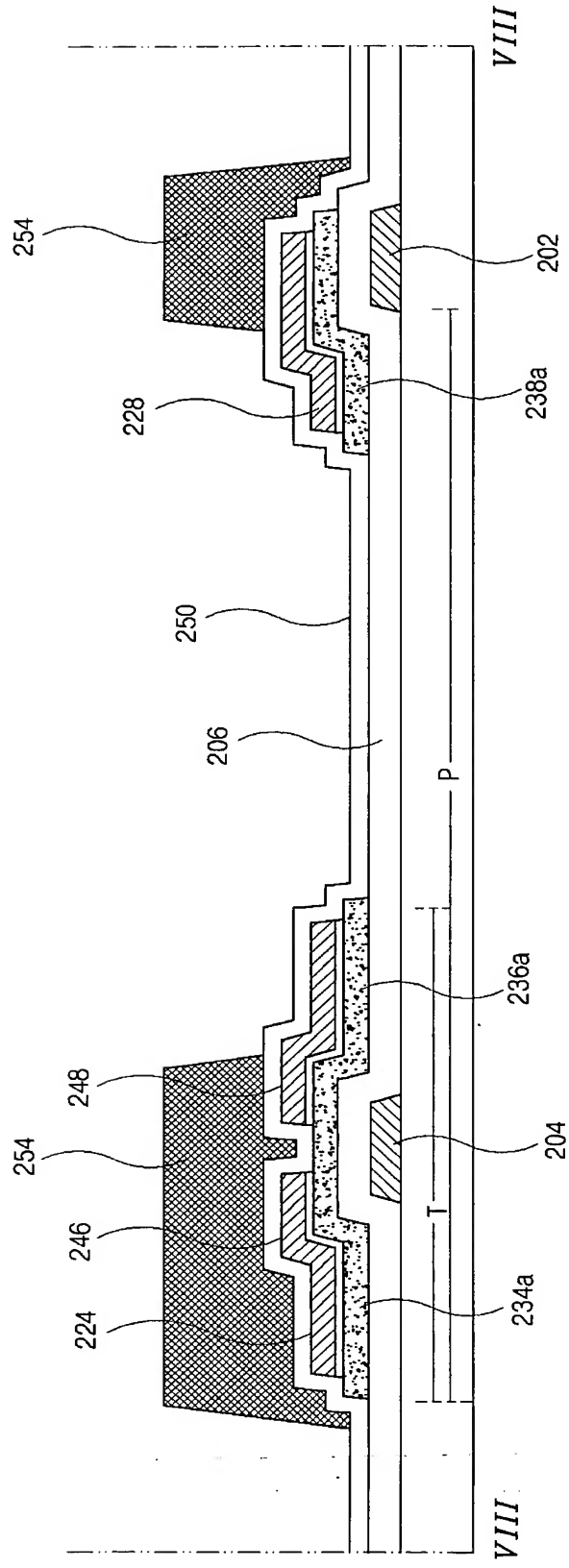


FIG. 8I

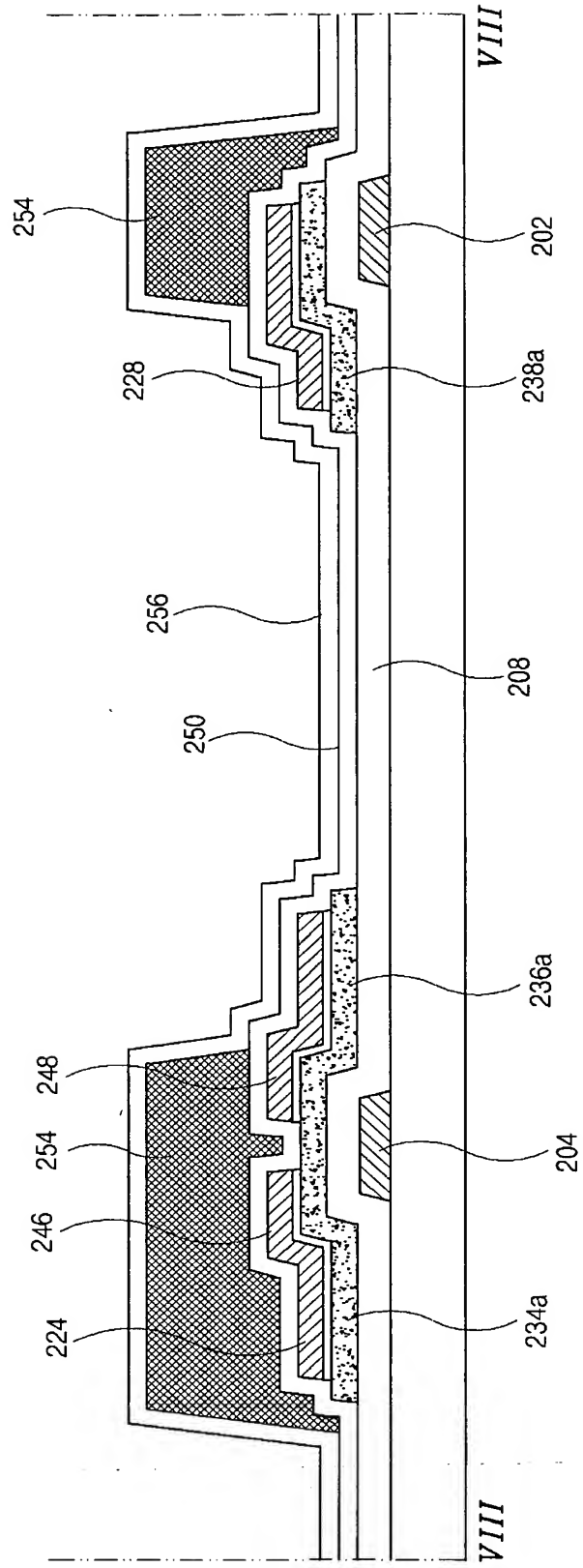


FIG. 8J

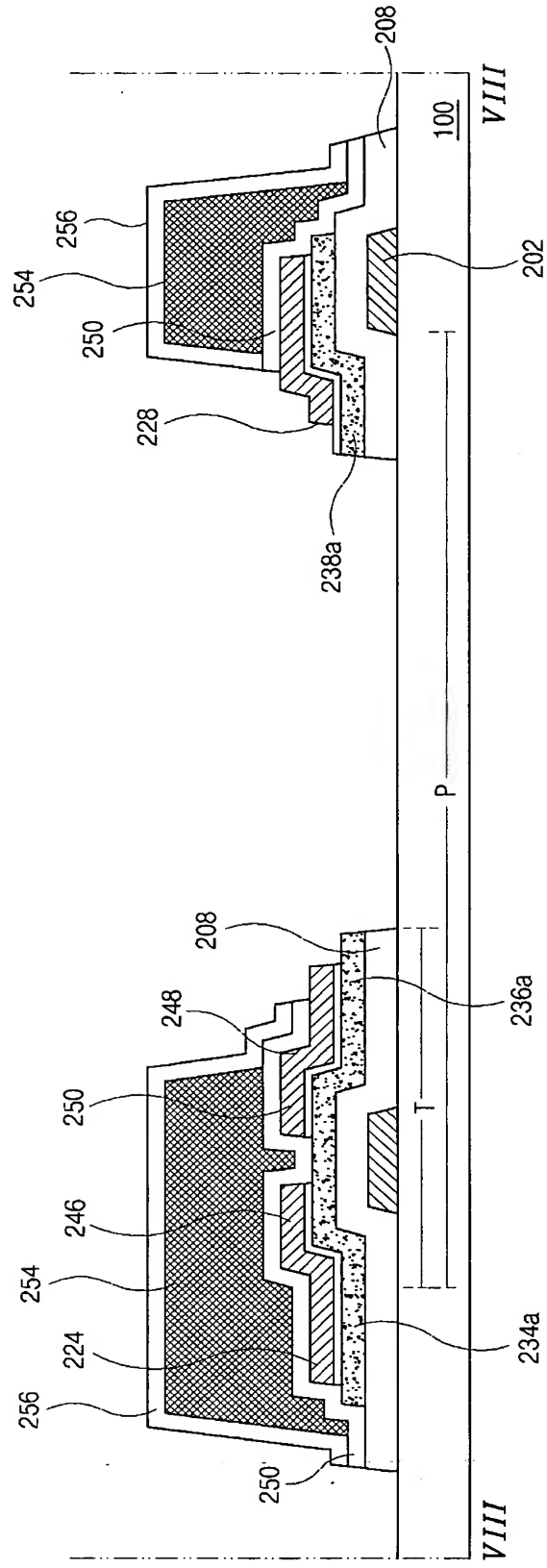


FIG. 8K

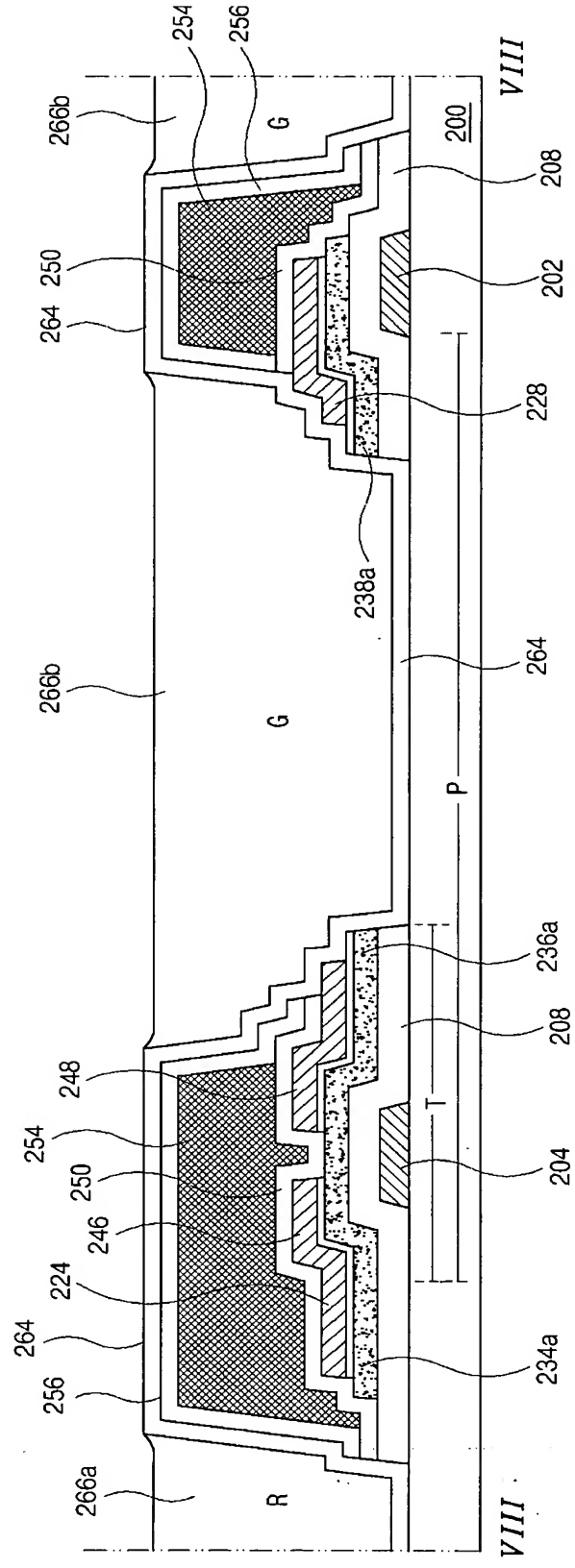


FIG. 8L

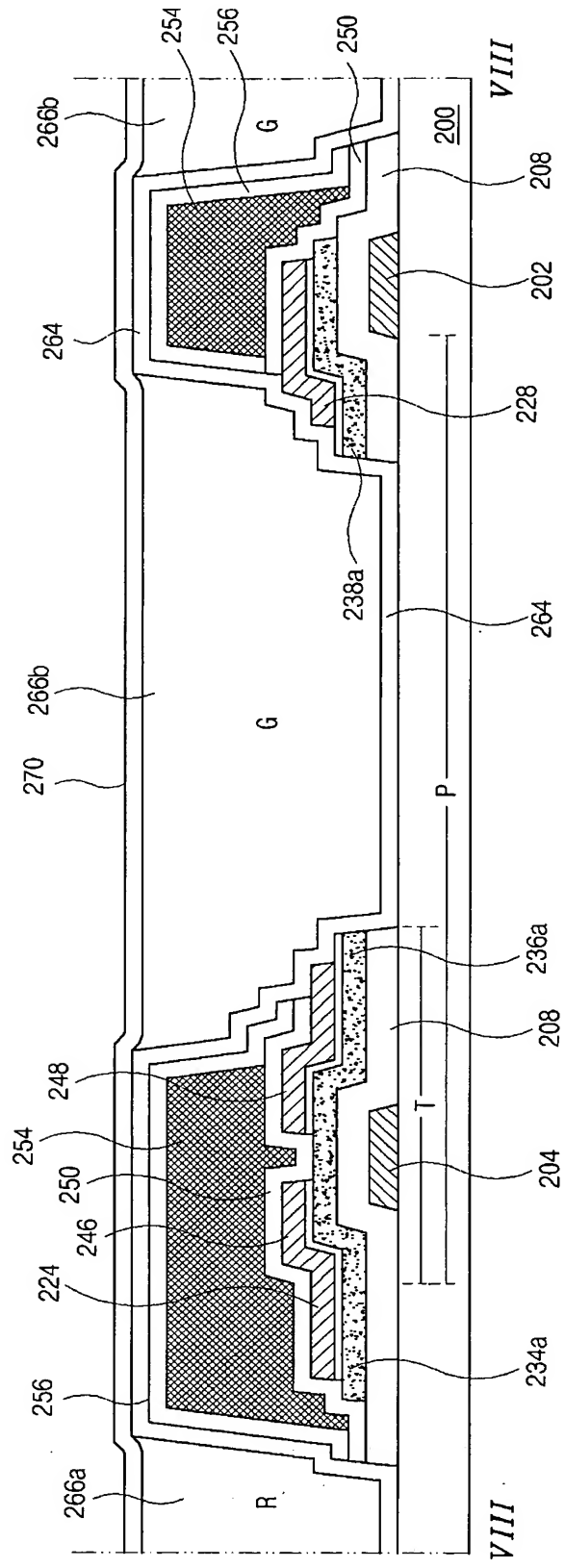


FIG. 9A

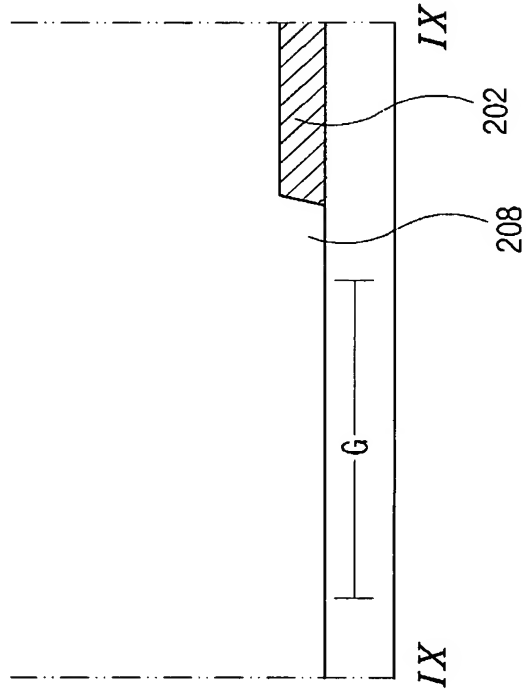


FIG. 9B

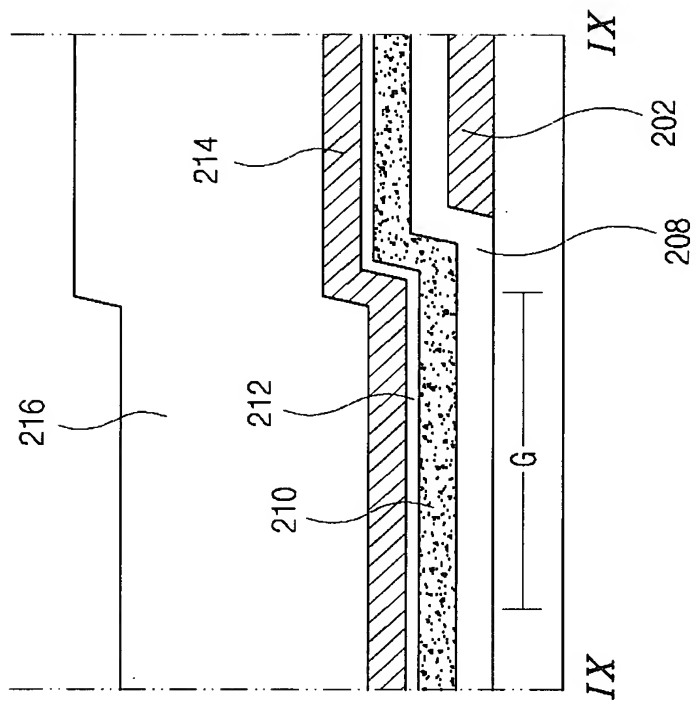


FIG. 9C

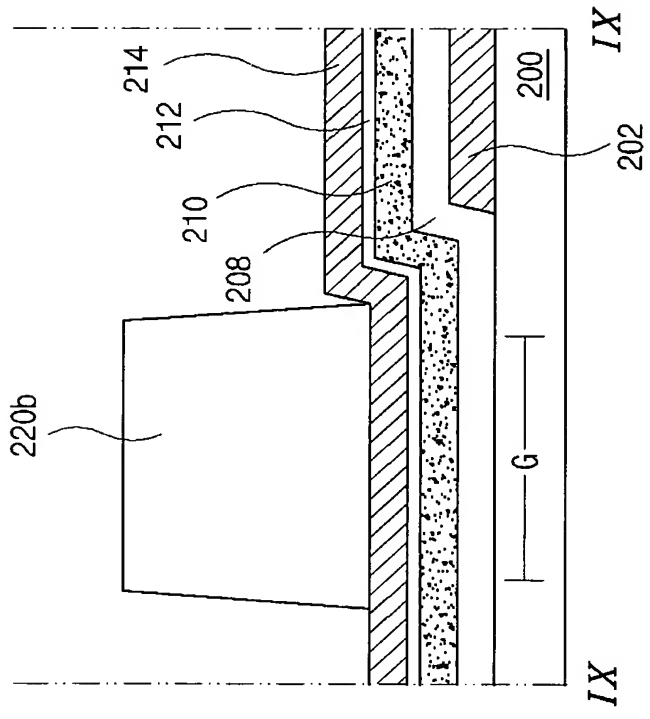


FIG. 9D

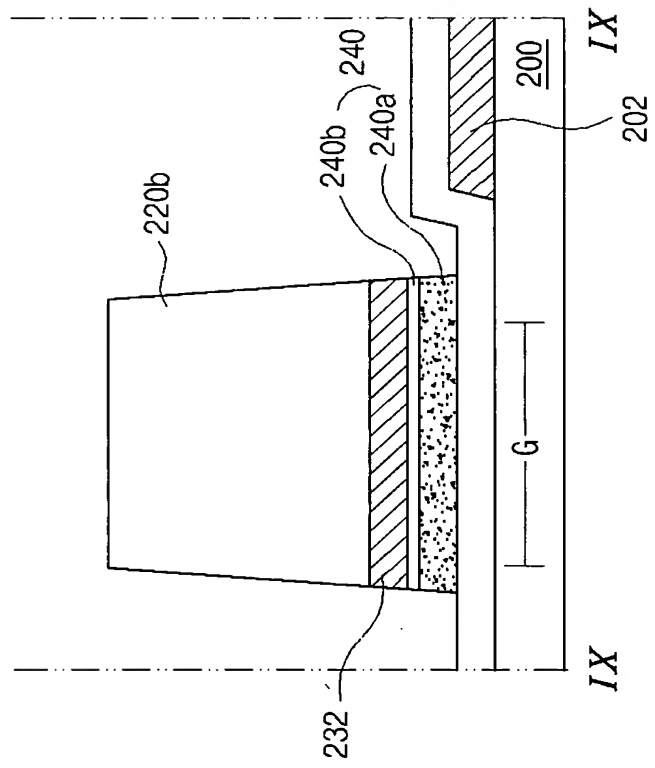


FIG. 9F

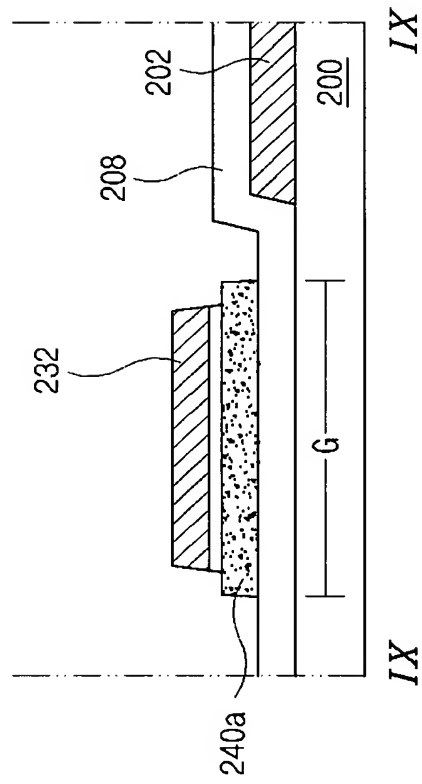


FIG. 9G

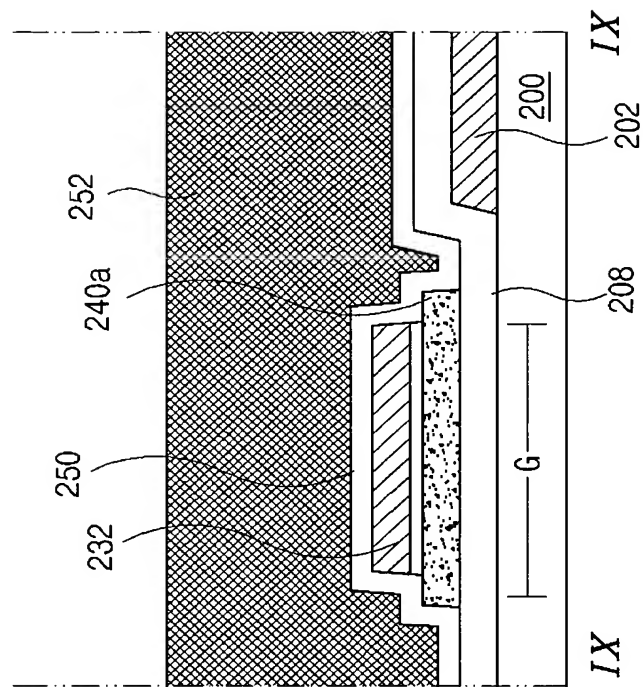


FIG. 9H

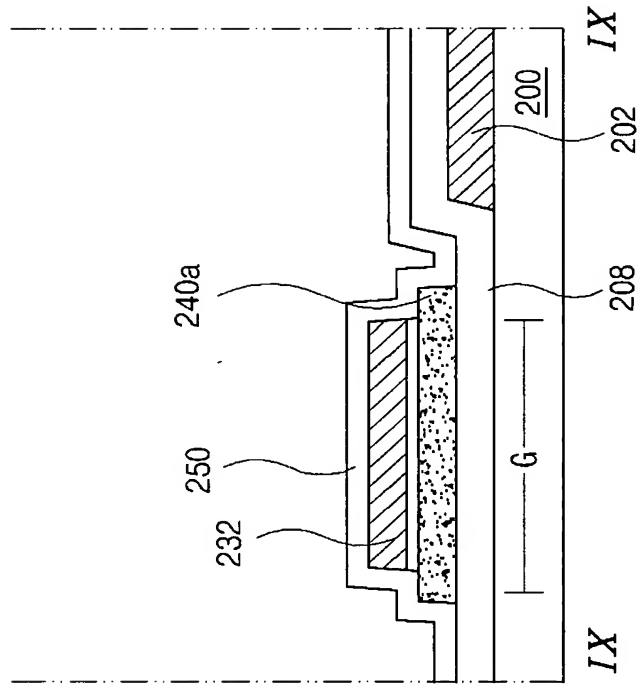


FIG. 9I

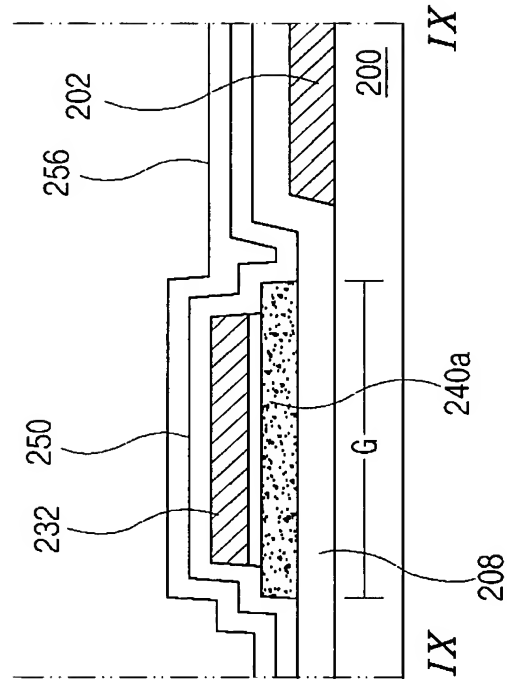


FIG. 9J

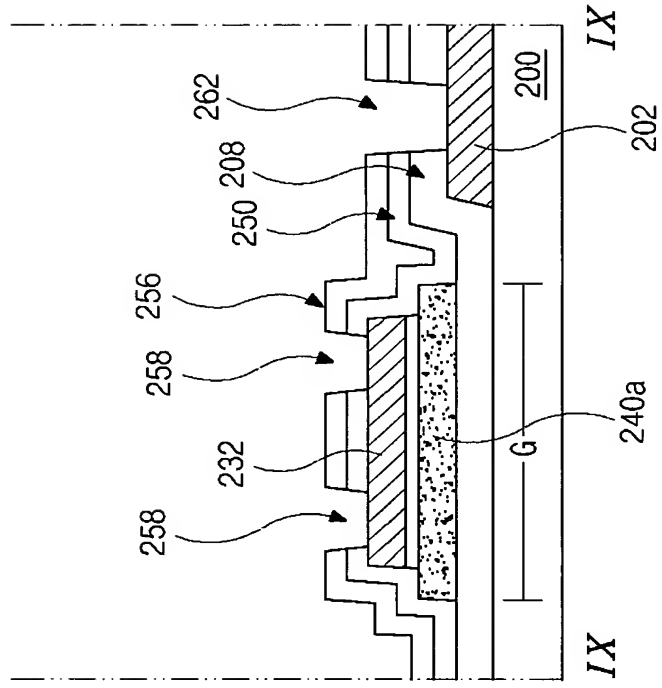


FIG. 9K

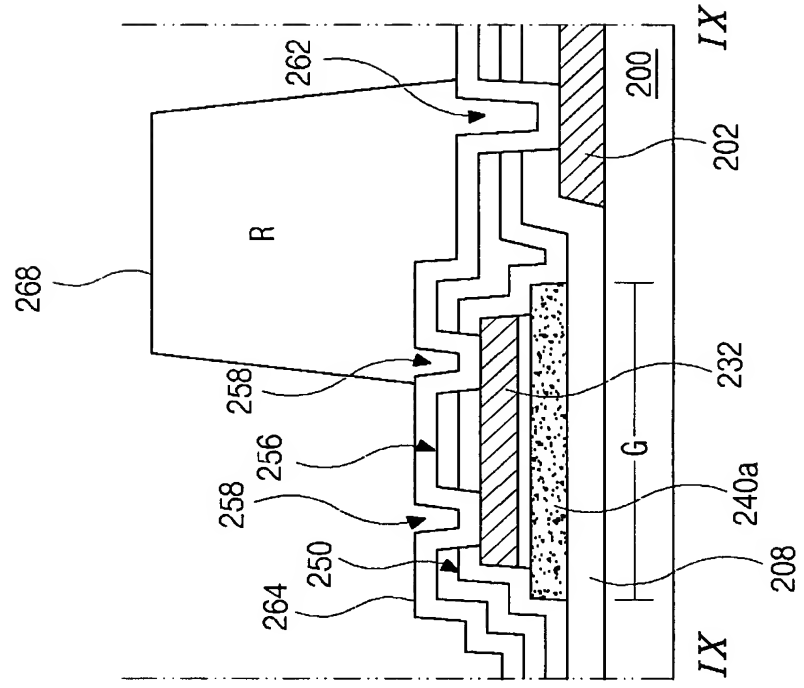


FIG. 9L

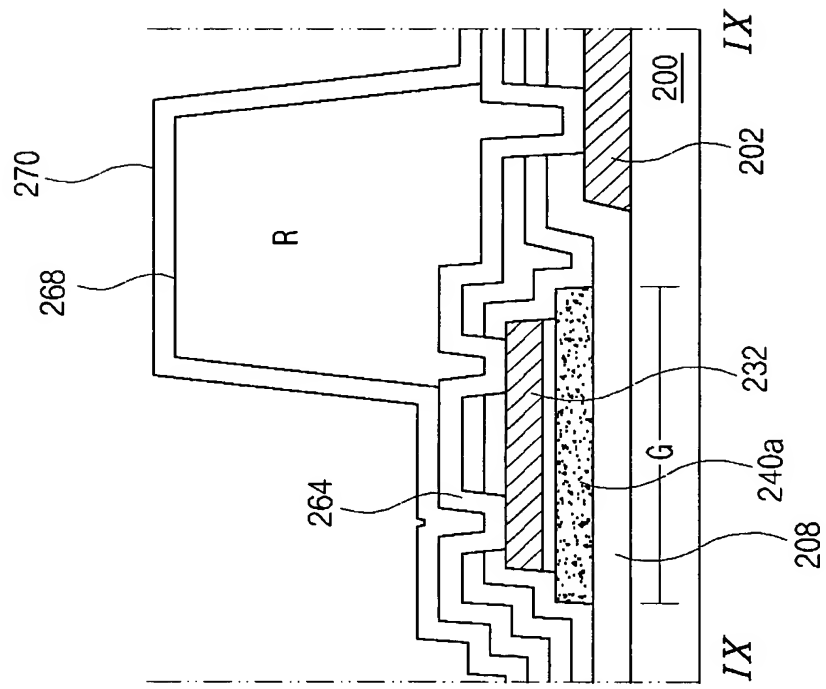


FIG. 9M

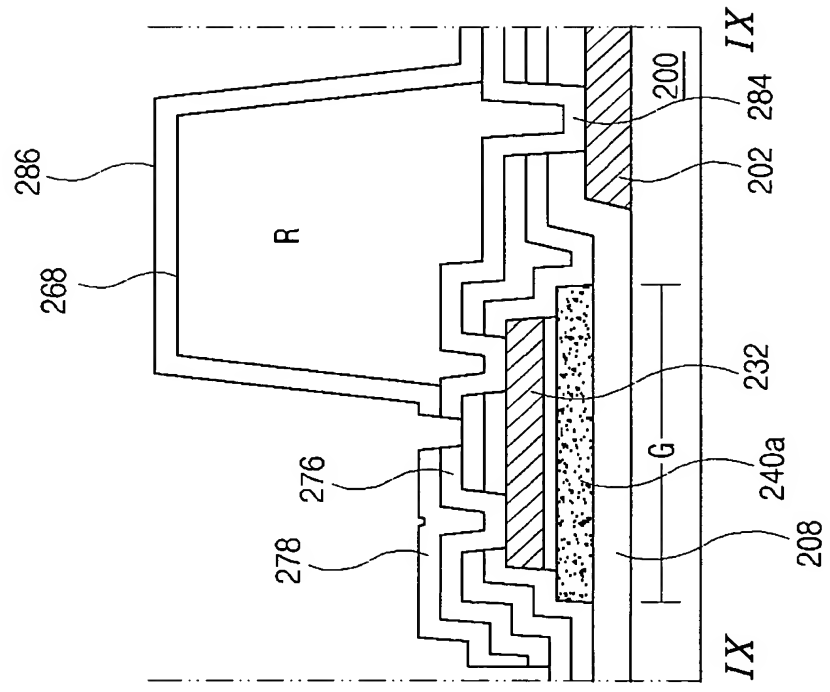


FIG. 10A

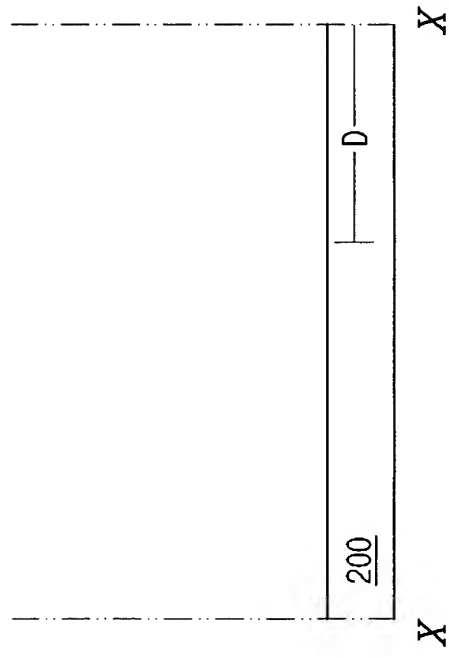


FIG. 10B

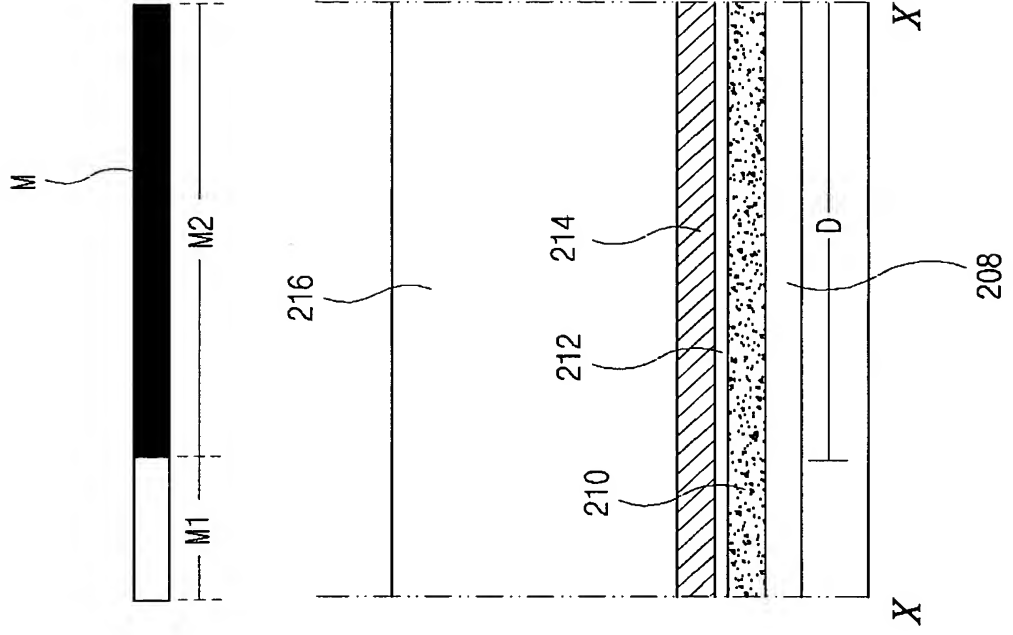


FIG. 10C

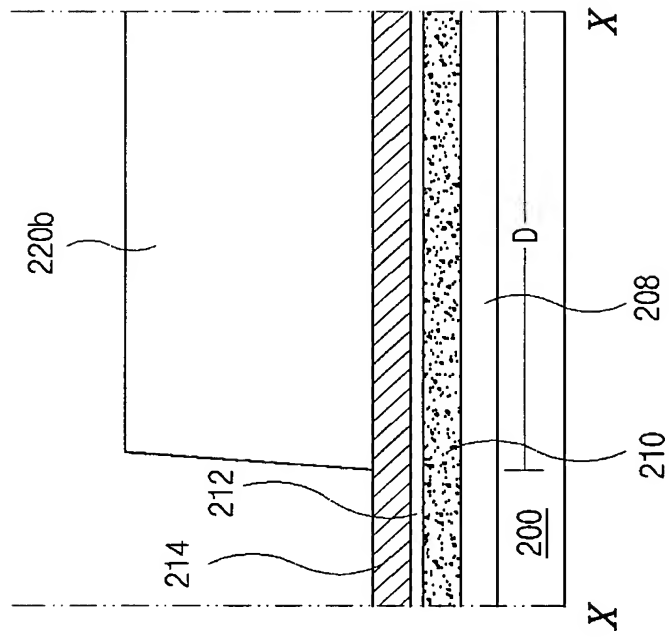


FIG. 10D

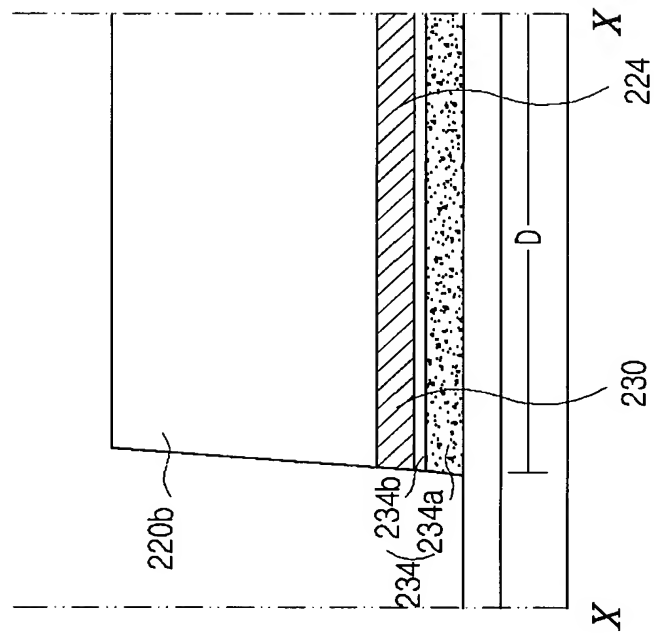


FIG. 10E

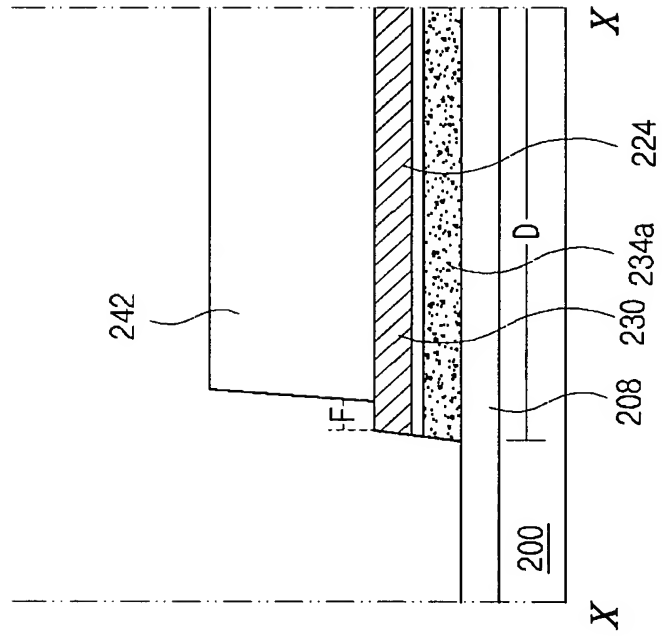


FIG. 10F

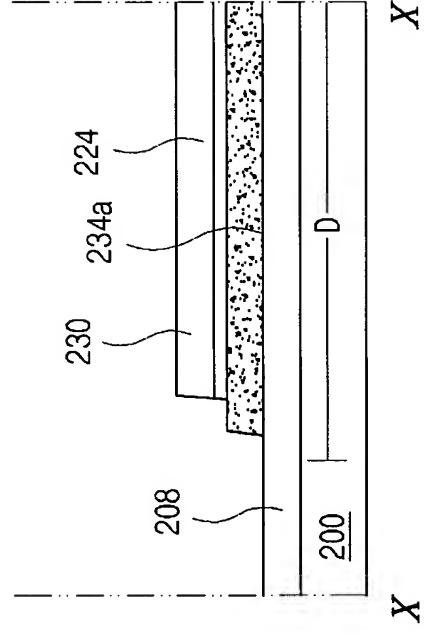


FIG. 10G

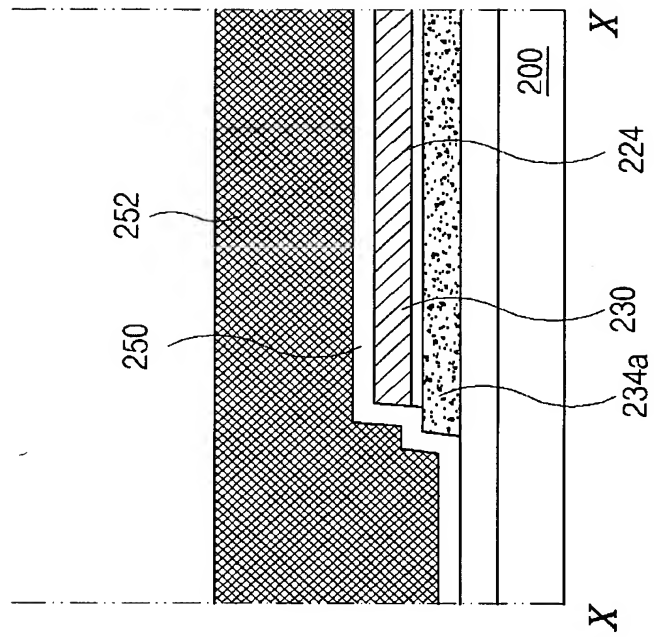


FIG. 10H

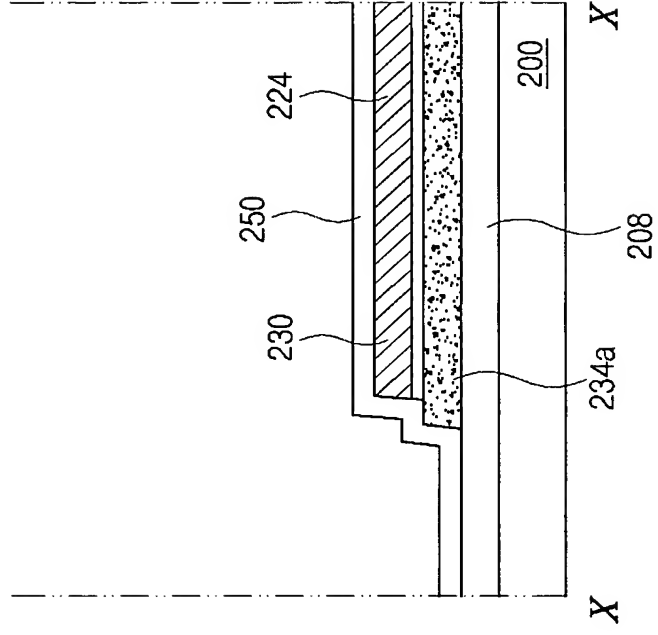


FIG. 10I

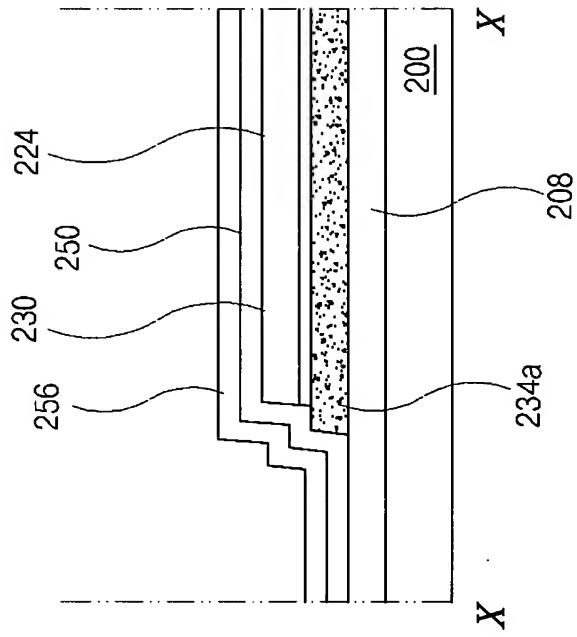


FIG. 10J

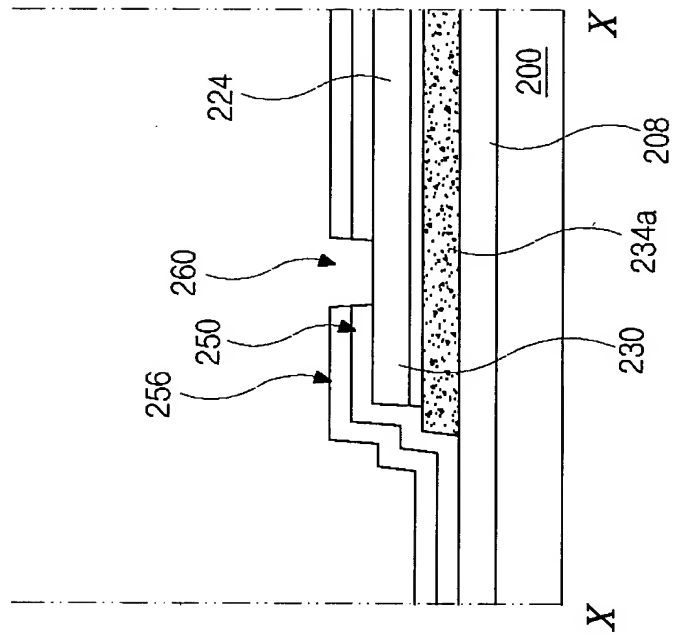


FIG. 10L

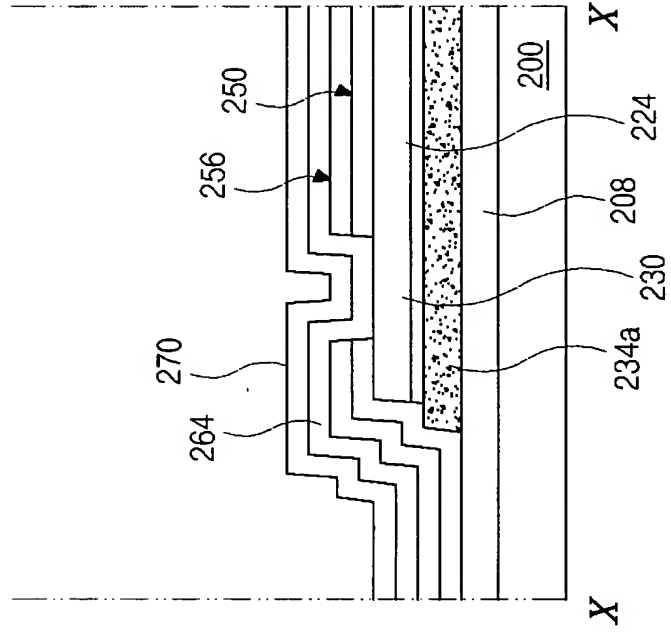


FIG. 11

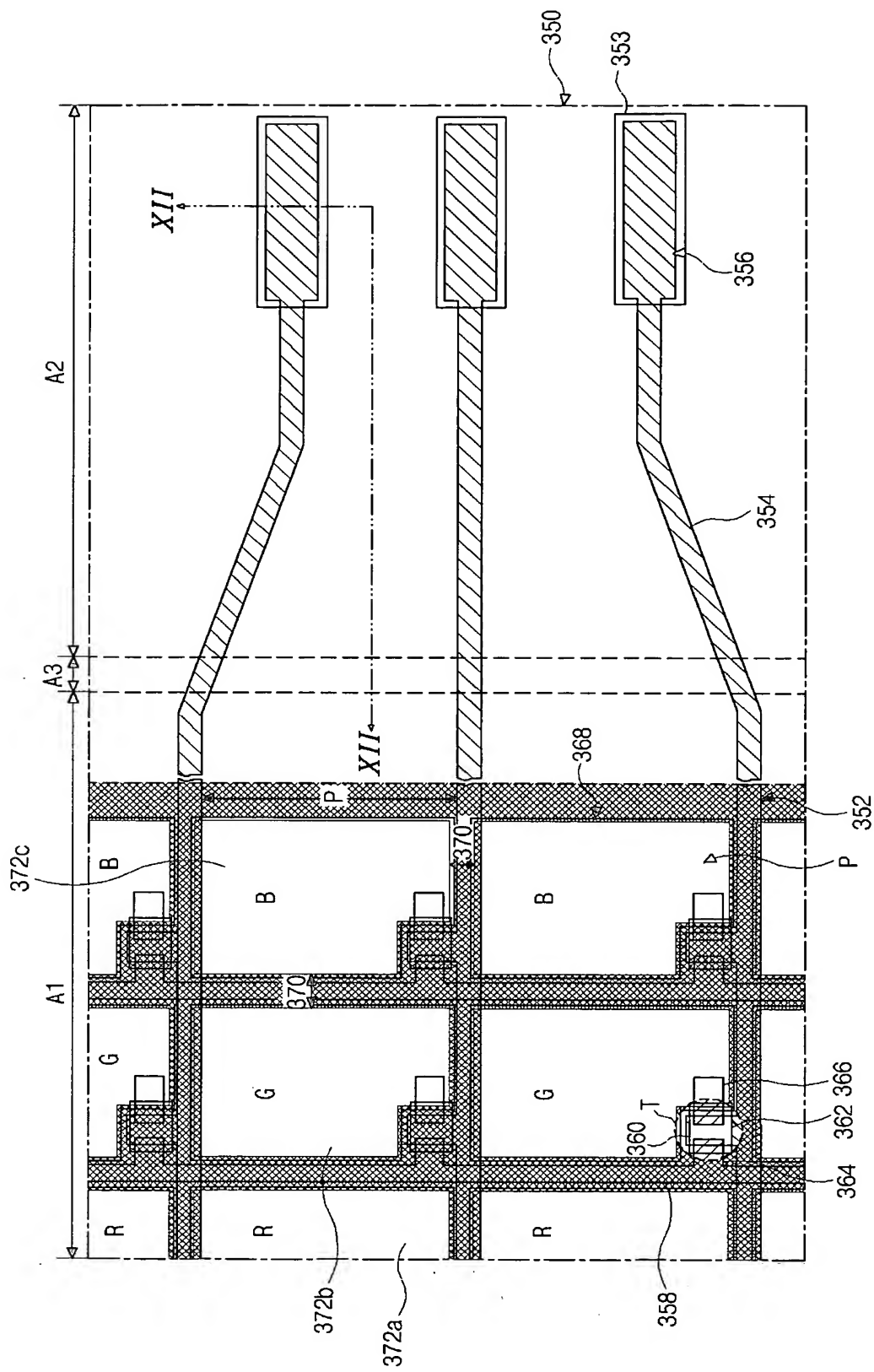


FIG. 12

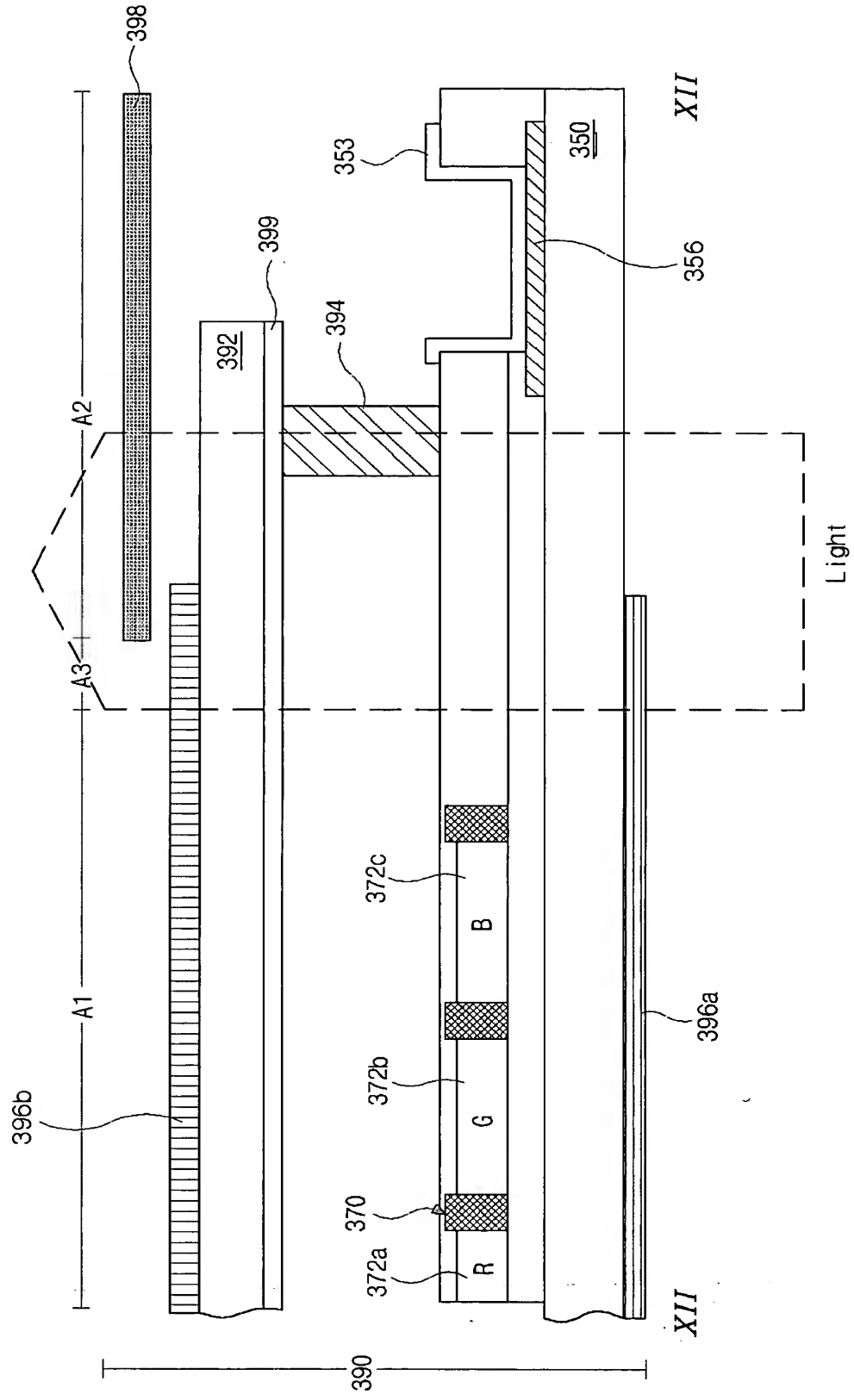


FIG. 13

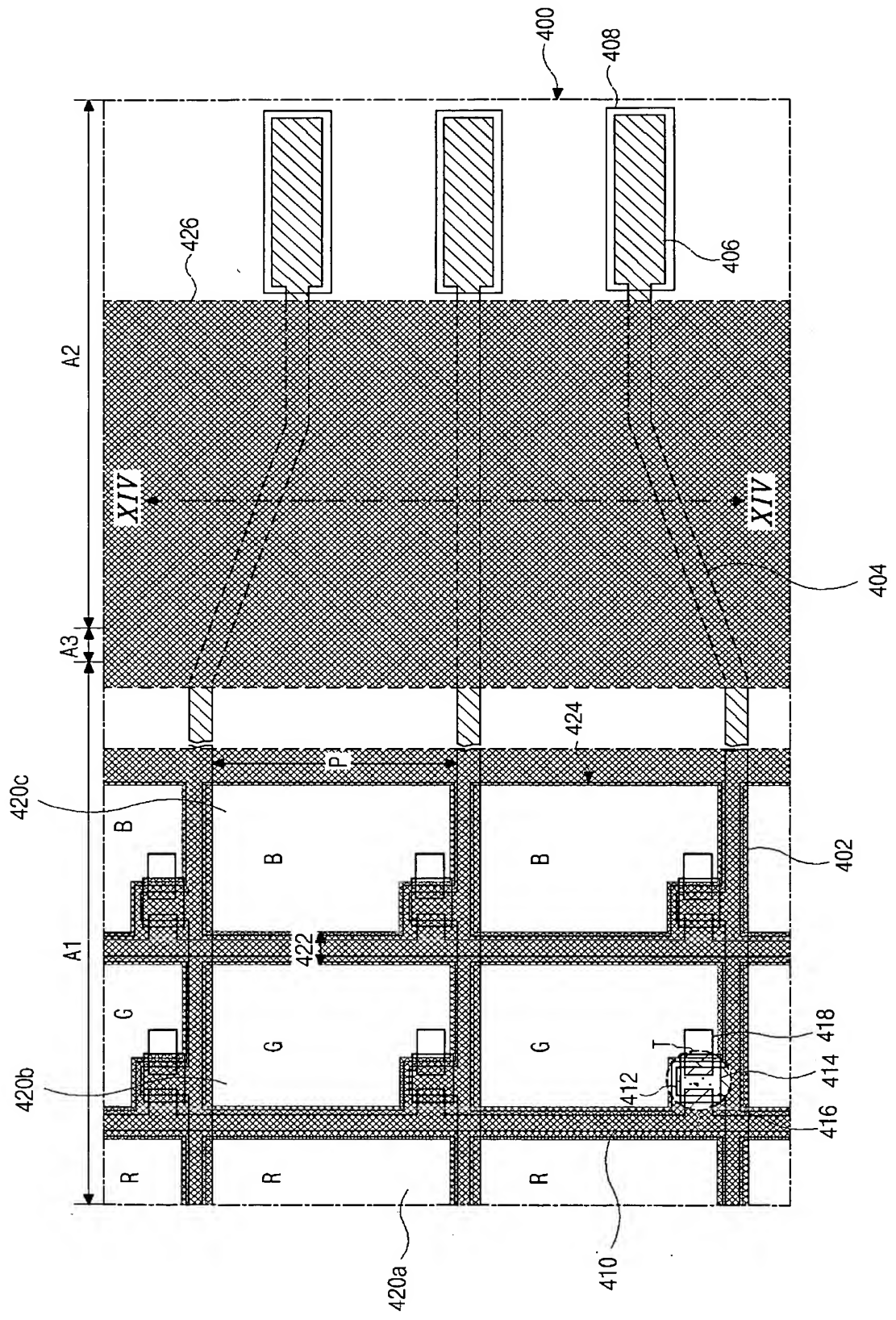


FIG. 14A

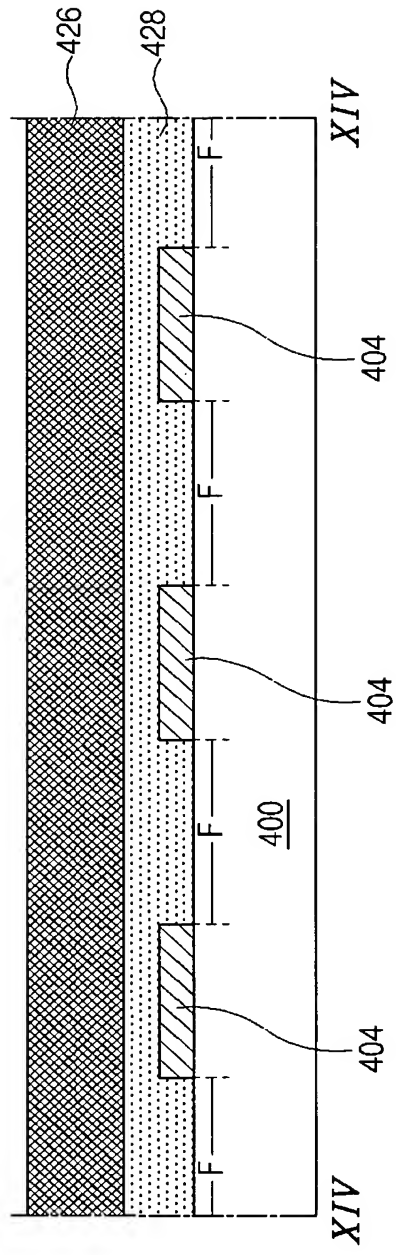
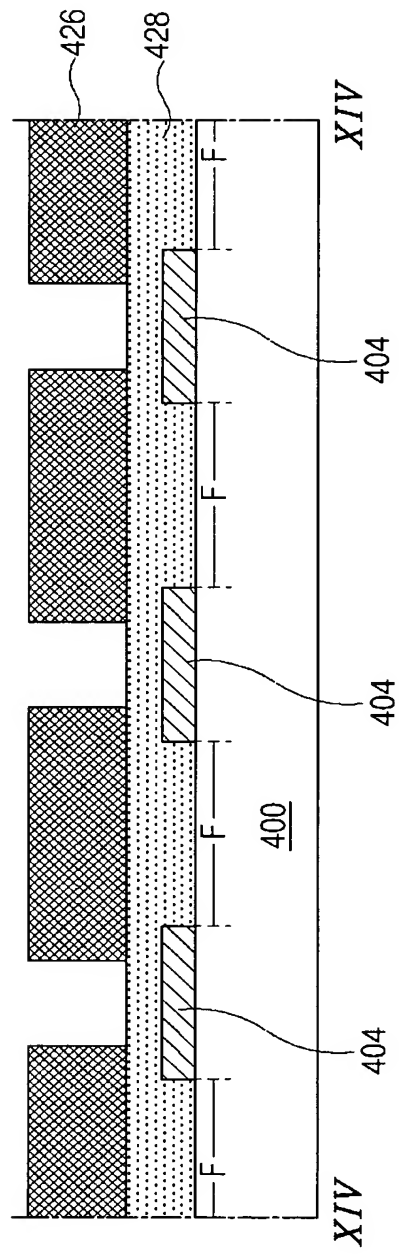


FIG. 14B



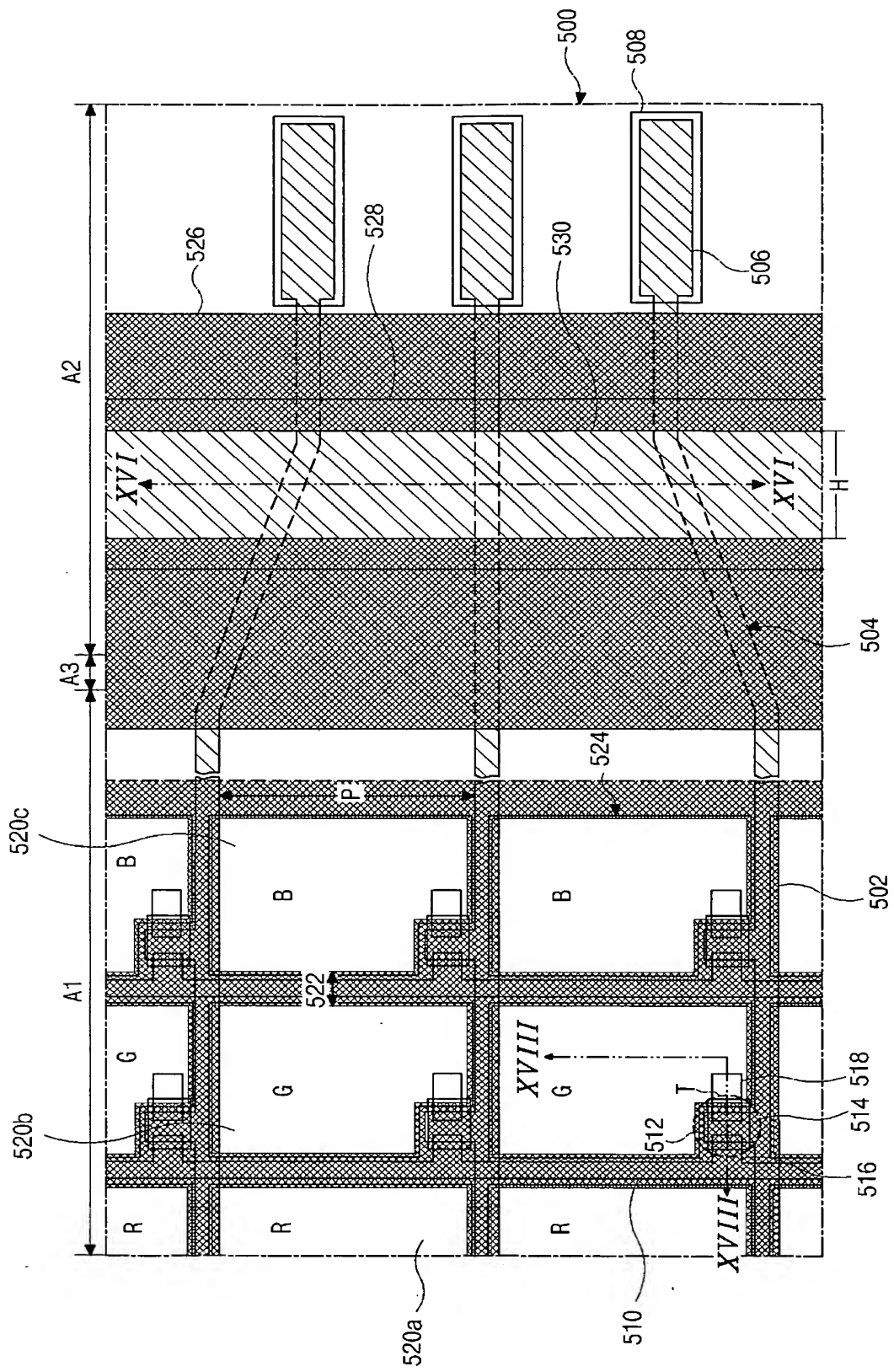
[illegible]

FIG. 16A

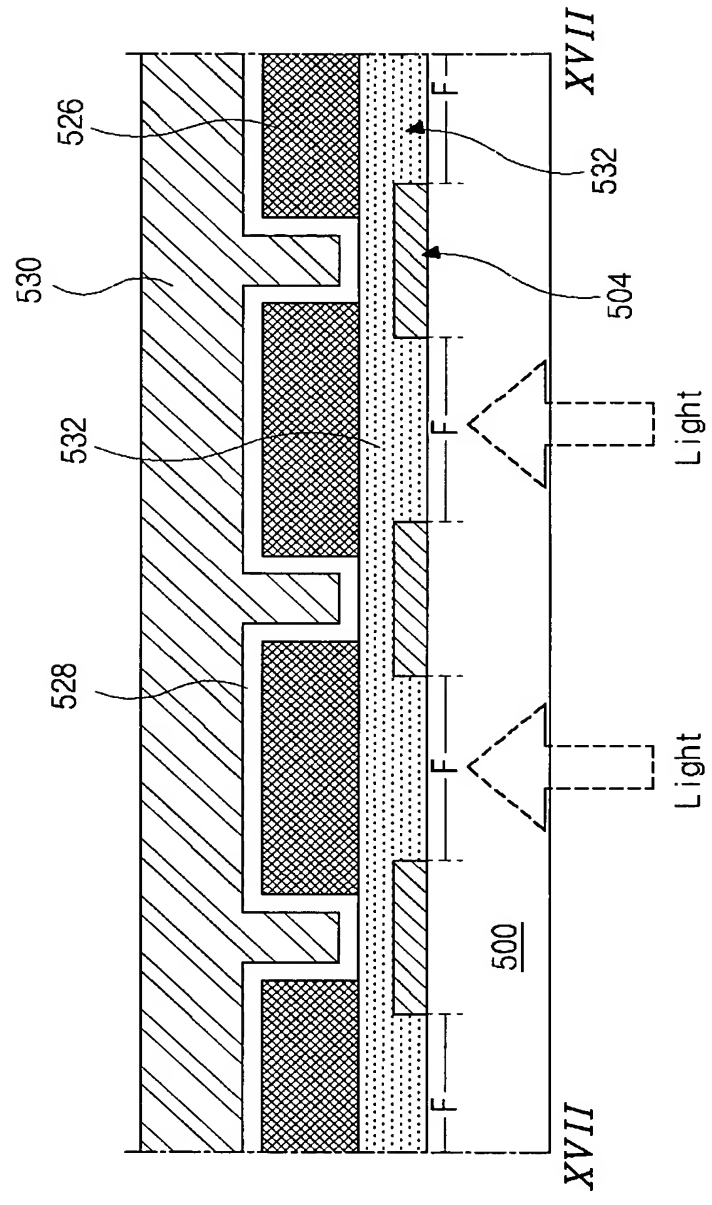


FIG. 16B

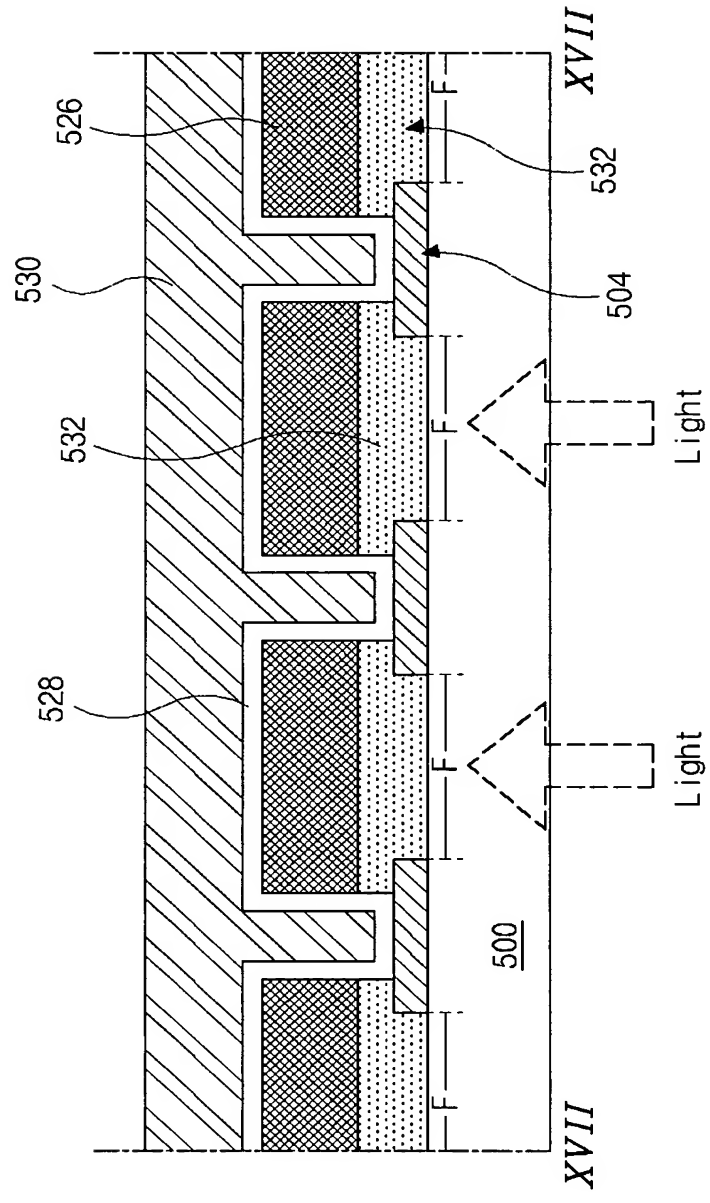


FIG. 18B

